

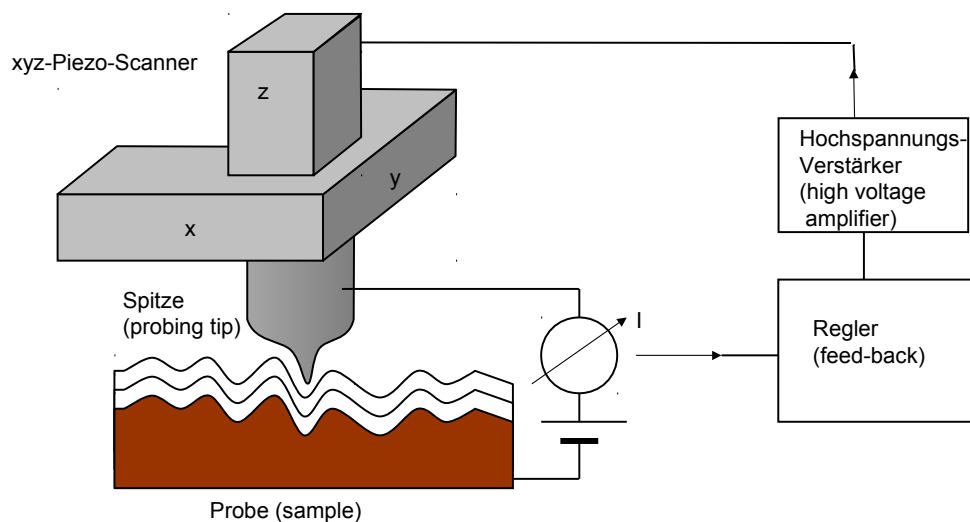
Nanostrukturen-Analysemethoden

Scanning Probe Microscopy

- **Scanning Tunneling Microscopy**
 - Tunneleffekt
 - G. Binnig and H. Rohrer, Nobelpreis 1986
 - Experimenteller Aufbau
- **Friction Force Microscopy**
 - Force Calibration
 - Atomic Stick Slip
 - Tomlinson Model
 - Nano-manipulation
- **Atomic Force Microscopy**
 - Short- and Long-Range Forces
 - Kelvin Probe Force Microscopy
 - Measurements on Semiconducting Devices
 - Molecules on Insulating Surfaces
 - Manipulation

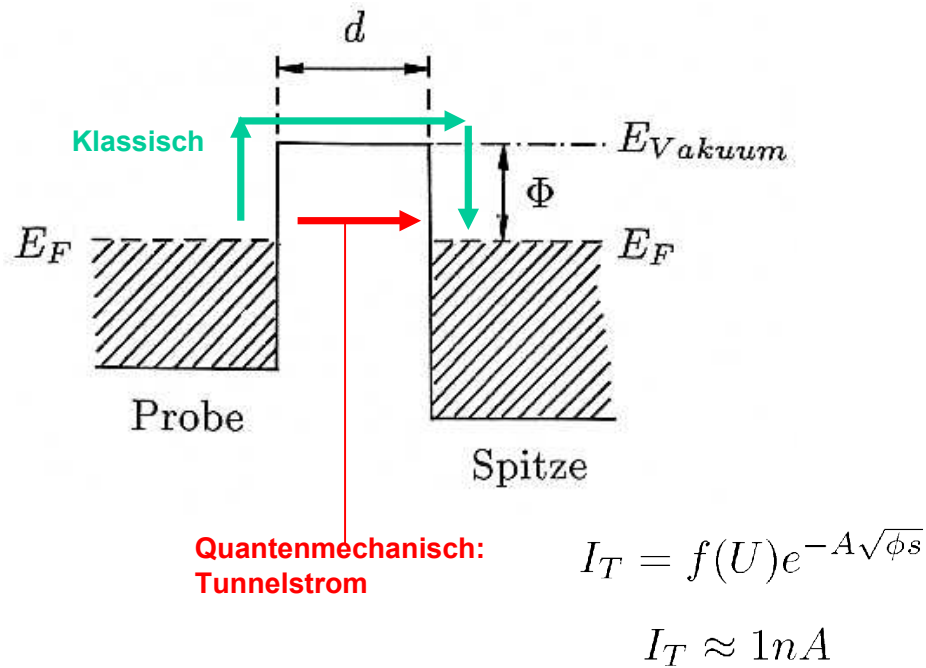
Thilo Glatzel, thilo.glatzel@unibas.ch
NANOLino Lab

Rastertunnelmikroskop (STM)



Ein Regler hält den Tunnelstrom (\approx pA-nA) zwischen Spitze und Probe konstant. Es werden Kontouren konstanten Tunnelstroms abgerastert.

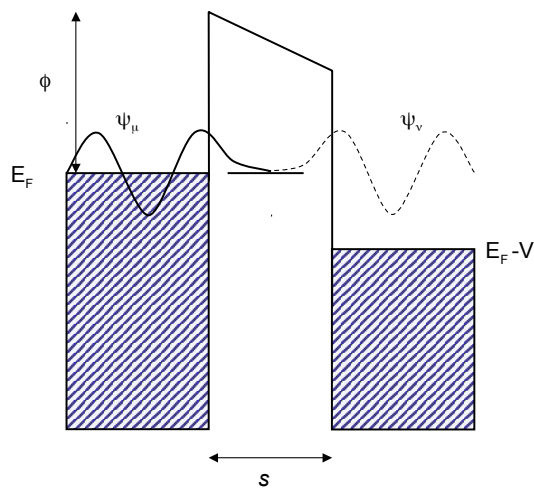
Tunneleffekt



J. Frenkel, *Phys. Rev.* **B 36**, 1604 (1930)

Tunneleffekt

Schon zu Beginn der Quantenmechanik wurde der Tunneleffekt vorausgesagt. Der Überlapp der Wellenfunktionen führt zu einer Transmission von Elektronen durch ein klassisch verbotenes Gebiet. Zwischen zwei Metallen, die durch Vakuum oder ein Oxid getrennt sind, fließt ein Tunnelstrom.



J. Frenkel, *Phys. Rev.* **B 36**, 1604 (1930)

Tunneleffekt

$$I_T = f(U)e^{-A\sqrt{\phi}s}$$

I_T : Tunnelstrom

U : Extern angelegte Spannung

s : Distanz zwischen Probe und Spitze

ϕ : Barrierenhöhe

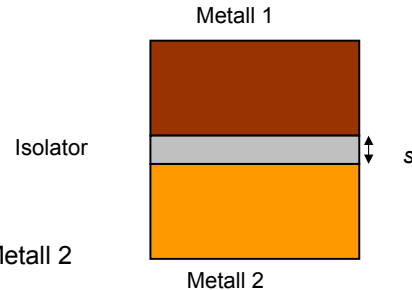
$$\phi \approx \frac{\phi_1 + \phi_2}{2} \quad \phi_1, \phi_2 \text{ Austrittsarbeiten von Metall 1 und Metall 2}$$

$$A = 2\sqrt{\frac{2m}{\hbar^2}} = 1.025 \text{ \AA}^{-1} \text{ eV}^{-1/2}$$

$f(U)$: Funktion der elektronischen Struktur von Probe und Spitze
Für freie Elektronen $f(U) \sim U$

Der Tunnelstrom hängt exponentiell vom Abstand s ab. Für typische Austrittsarbeiten von $\approx 4.5 \text{ eV}$ ändert sich der Strom etwa um eine Größenordnung, wenn die Distanz um 1 \AA verändert wird. Historisch wurde zuerst das Oxidtunneln realisiert. Erst mit dem STM konnte Vakuumtunneln beobachtet werden.

J. Frenkel, *Phys. Rev.* **B 36**, 1604 (1930)



Scanning Tunneling Microscope (STM)



Source: IBM



G. Binnig and H. Rohrer
Nobelpreis 1986

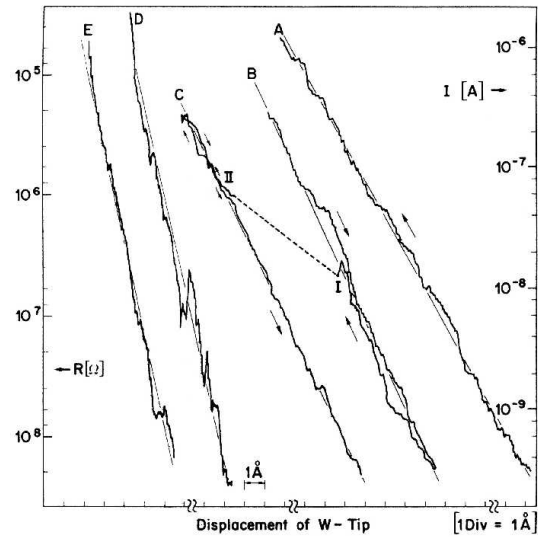
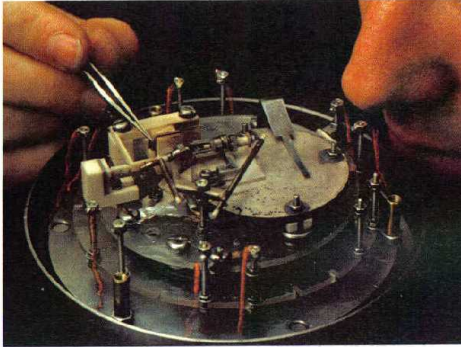
IBM Rüschlikon
Switzerland

G. Binnig, H. Rohrer, Ch. Gerber, and E. Weibel, *Phys. Rev. Lett.* **50**, 120 - 123 (1983)

G. Binnig, H. Rohrer, Ch. Gerber, and E. Weibel, *Phys. Rev. Lett.* **49**, 57 - 61 (1982)

G. Binnig, H. Rohrer, Ch. Gerber, and E. Weibel, *Appl. Phys. Lett.*, Vol. 40, Issue 2, pp. 178-180 (1982)

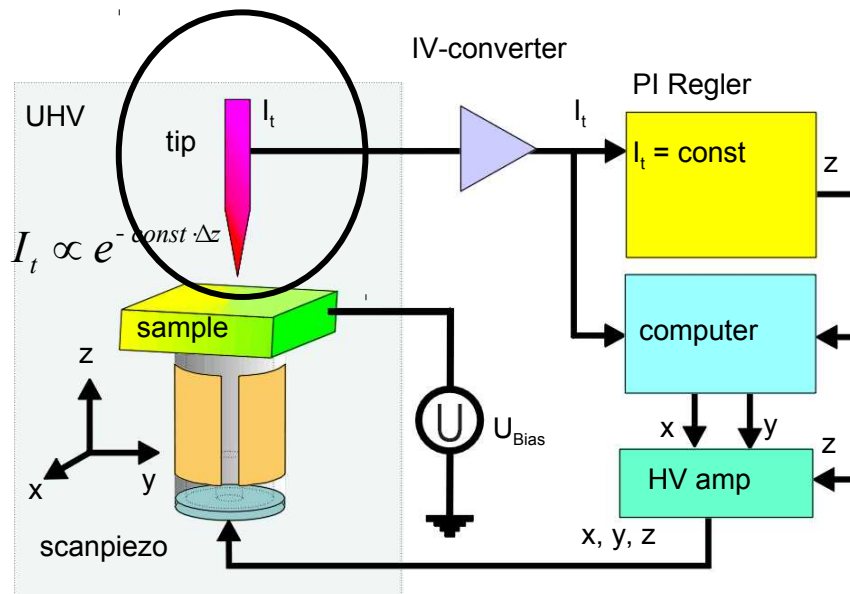
Scanning Tunneling Microscopy (STM)



Exponentieller Abfall des Tunnelstromes mit dem Abstand

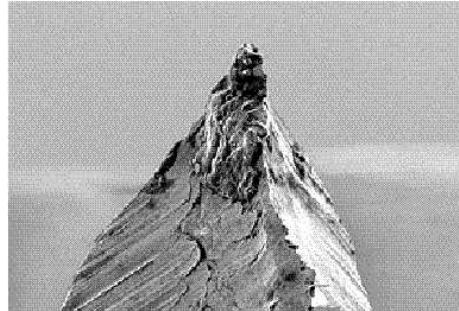
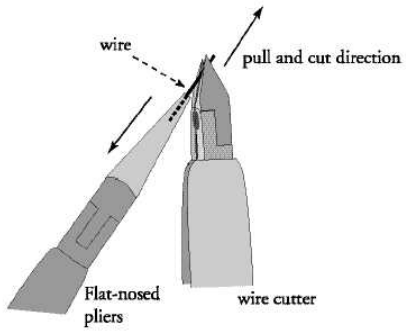
G. Binnig, H. Rohrer, Ch. Gerber, and E. Weibel, Appl. Phys. Lett., Vol. 40, Issue 2, pp. 178-180 (1982)

Blockschaltbild STM



Spitzen

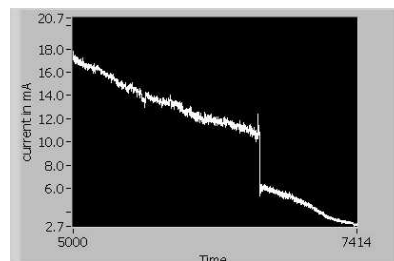
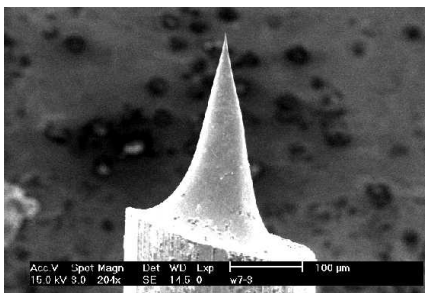
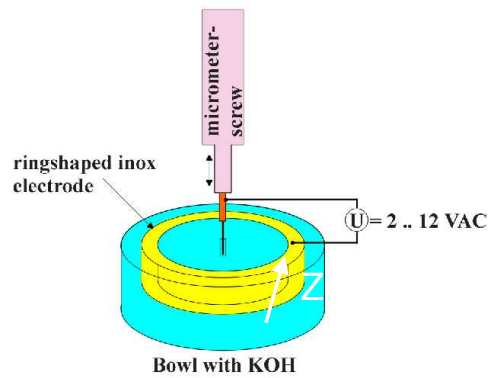
1. Abgerissener PtIr Draht



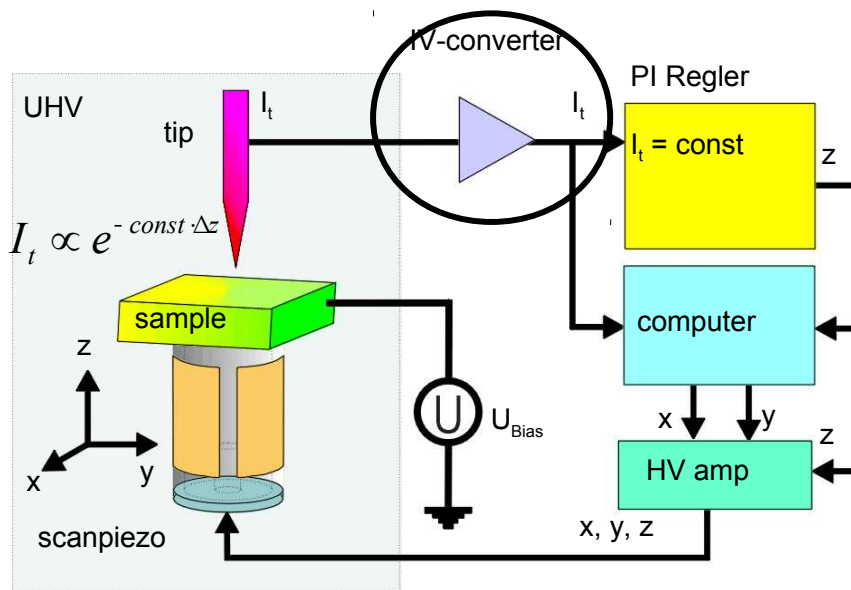
Oder...

Spitzen

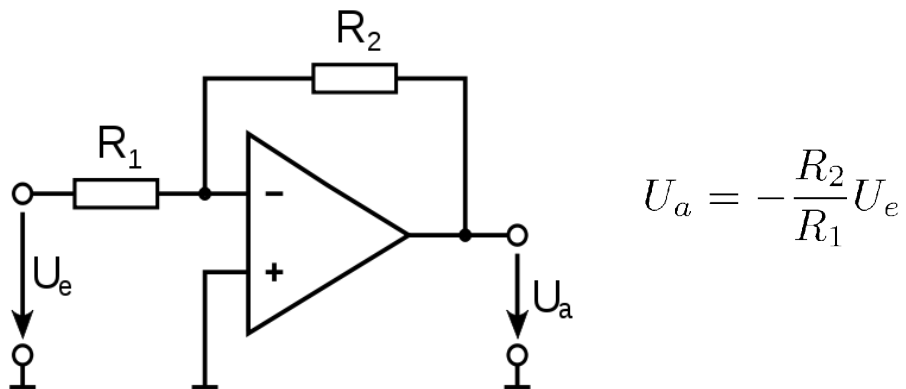
2. Elektrochemisch geätzte Wolframspitzen:



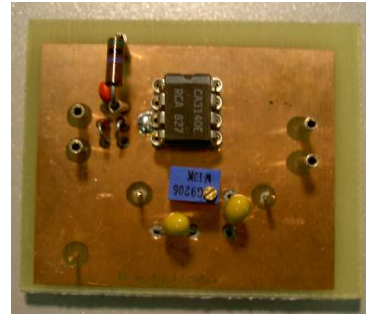
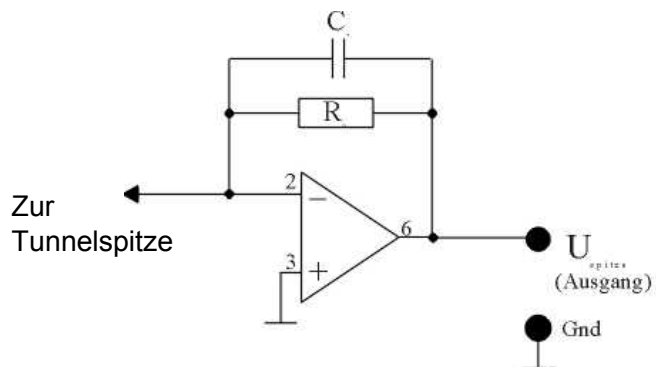
Blockschaltbild STM



Invertierender Verstärker



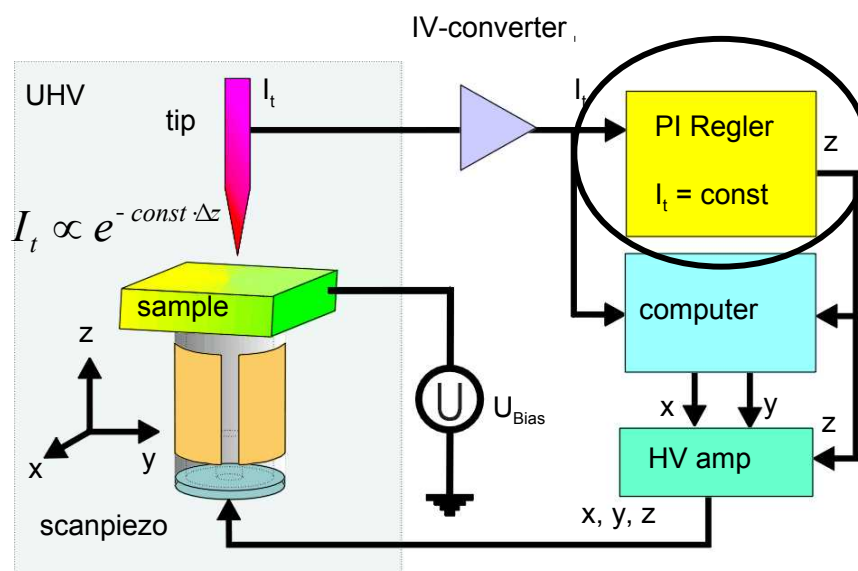
Strom-Spannungswandler



$$U_A = - R \cdot I_t$$

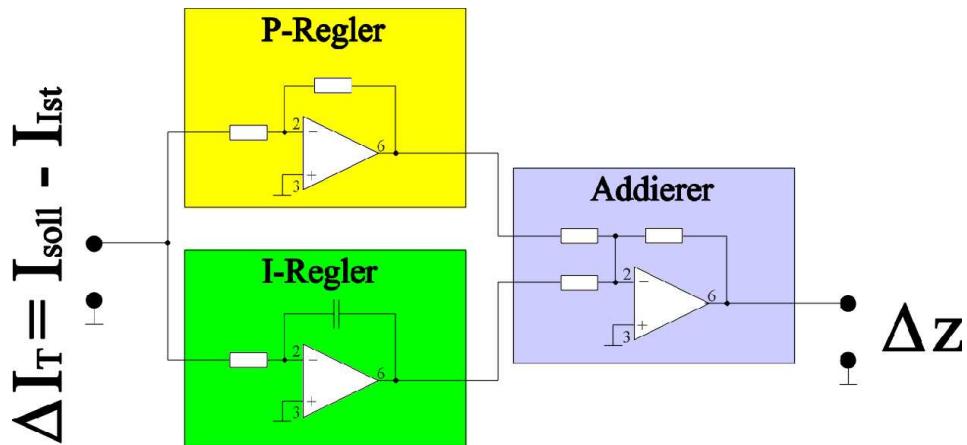
Bei $R = 100\text{M}\Omega$ entspricht $U_A = 1\text{V}$
einem Tunnelstrom von 10nA

Blockschaltbild STM

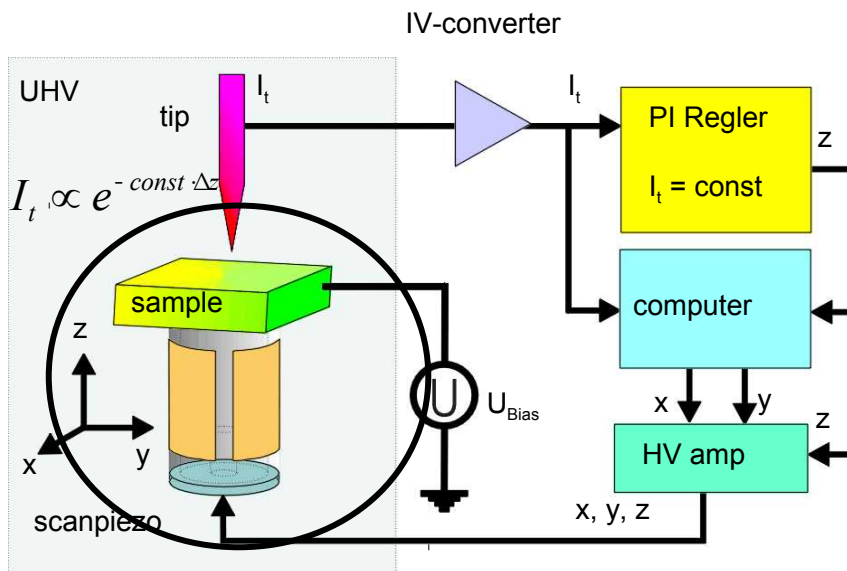


PI Regler

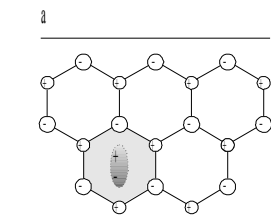
Regelt den Abstand Spitze-Probe so, dass der Tunnelstrom konstant bleibt



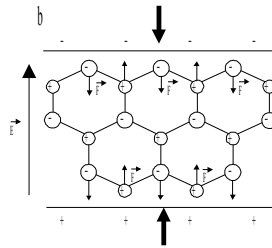
Blockschaltbild STM



Piezos



Verschiedene
Ladungsschwerpunkte



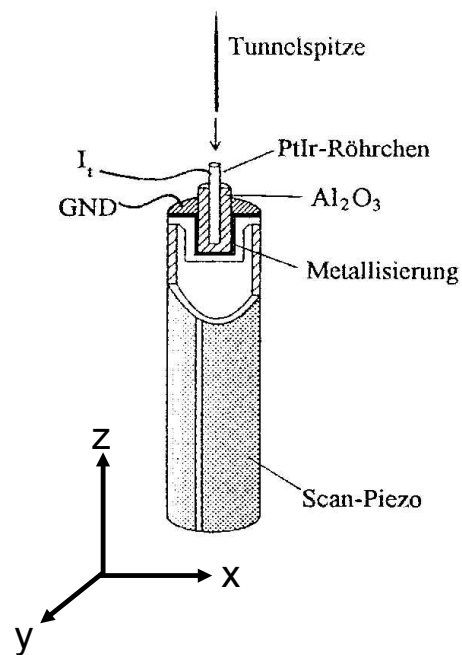
Verformung
durch
Anlegen einer
elektrischen
Spannung

Typische Piezoelektrische Materialien:

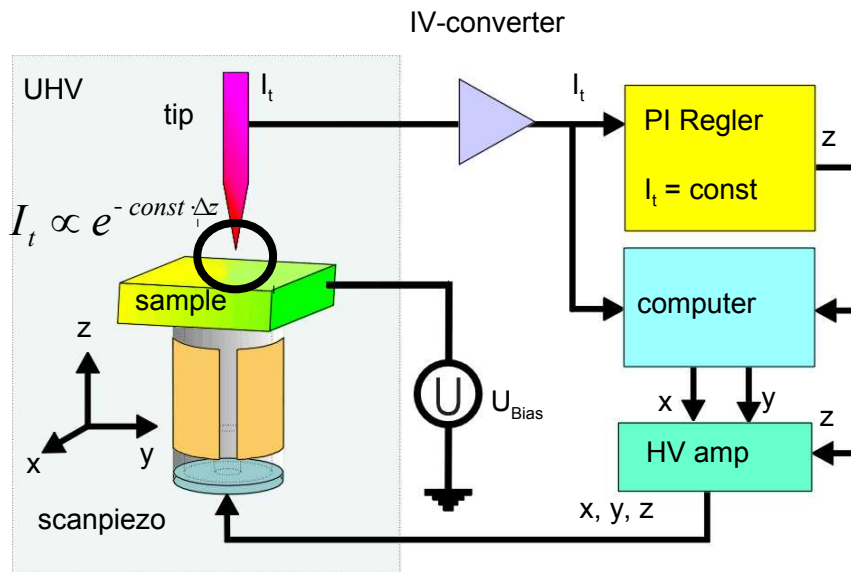
- Quarz
- Bariumtitanat
- Bleizirkontitanat (PZT)
- Etc.

Piezo tubes

XYZ-Stellglieder

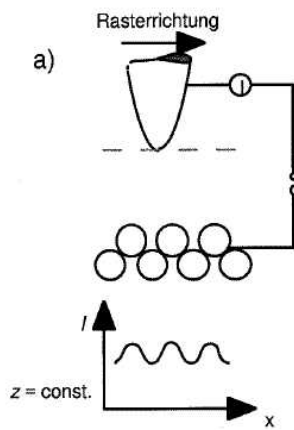


Blockschaltbild STM

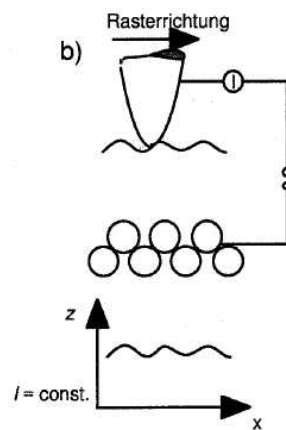


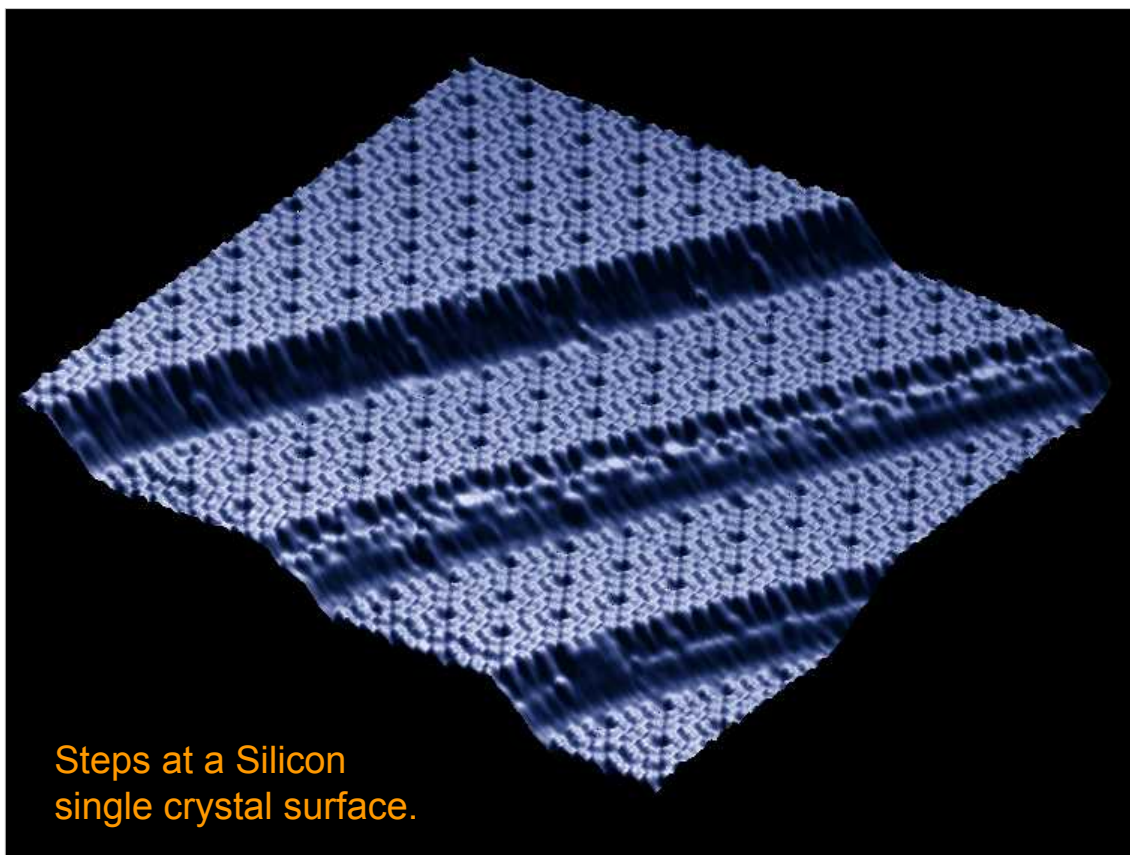
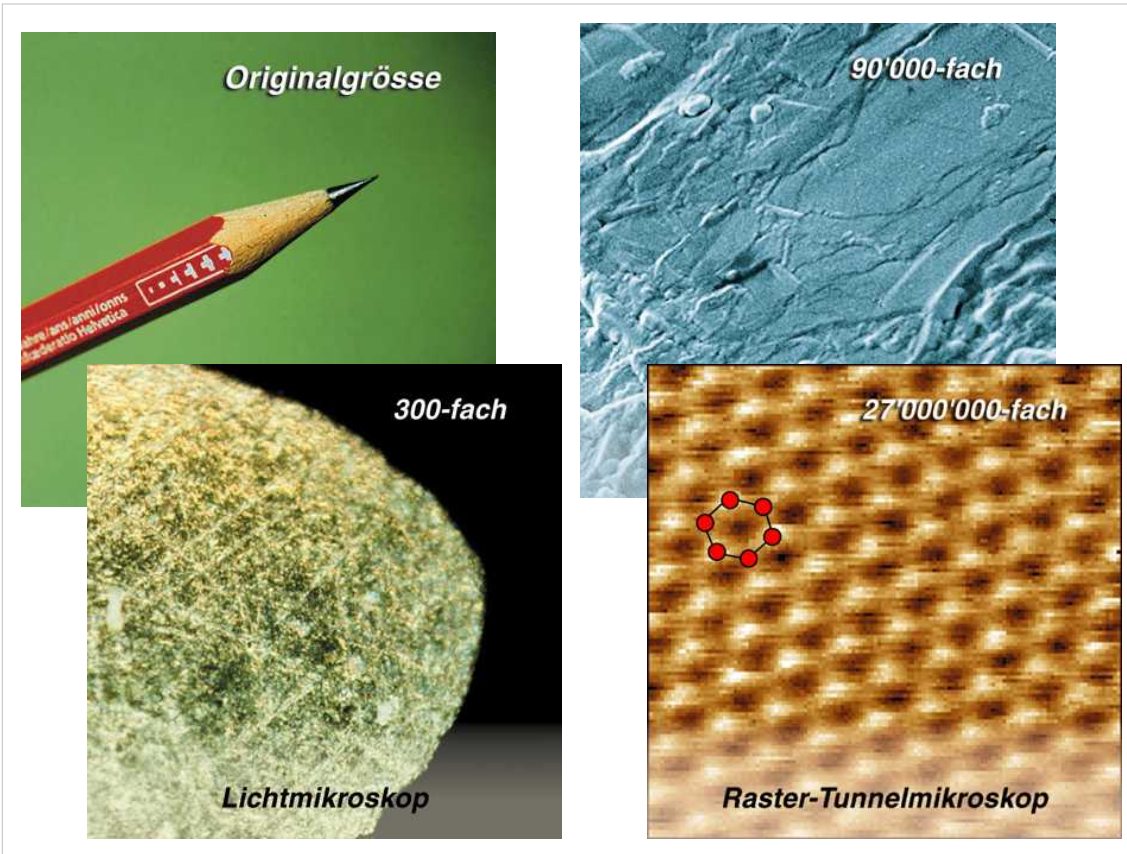
Messmodi

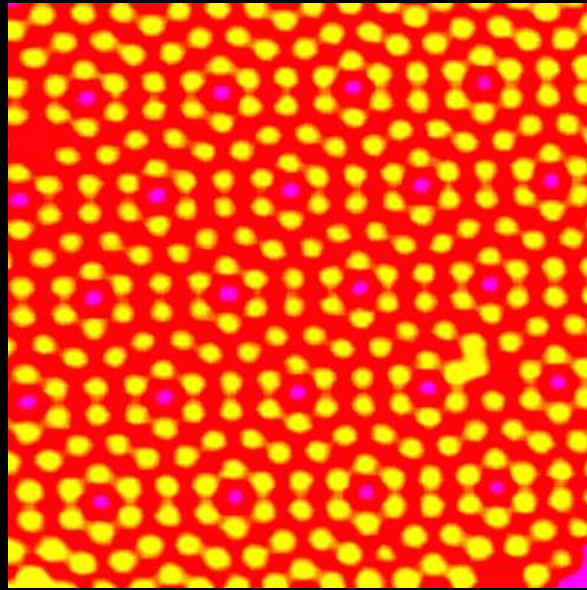
Constant Height



Constant Current



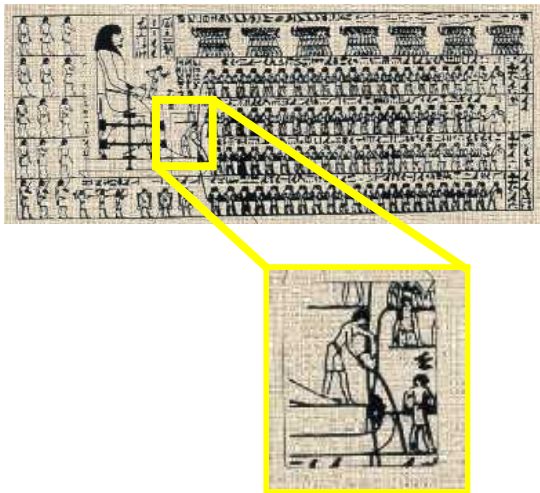




Si(111)7x7 reconstructed surface

Importance of Friction

Long time ago...

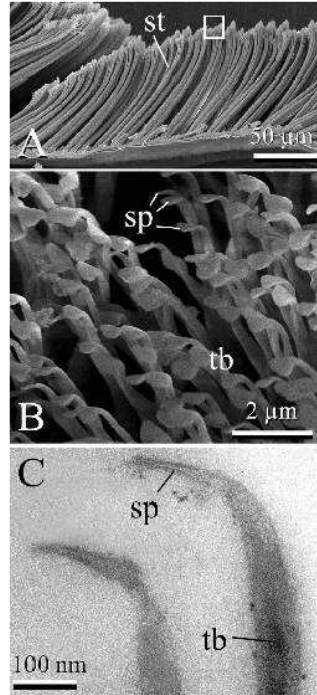


Nowadays...



In all cases: It is highly desirable to reduce and control friction

Gecko uses nanometer-sized contacts to climb walls

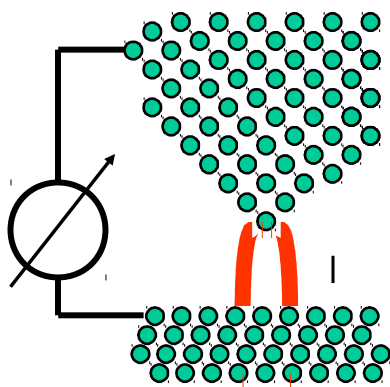


Gecko is able to control the contact area on all length scales

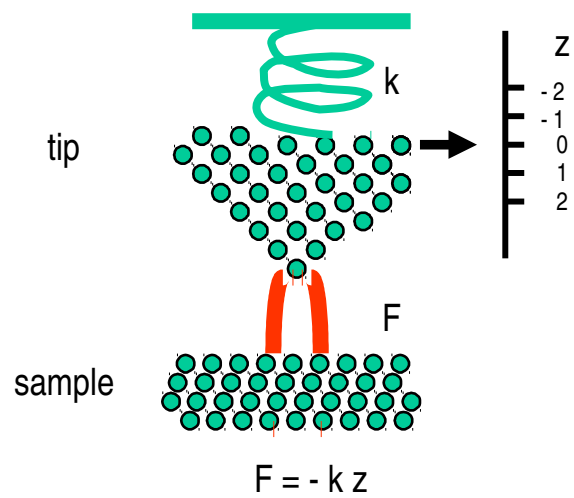
From B. Persson and S. Gorb
JCP, 119, 11437 (2003)

Scanning X Microscopy

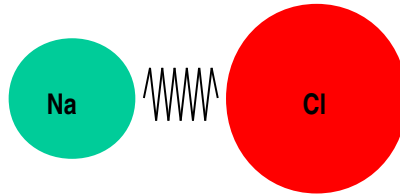
S Tunneling M



S Force M



Kräfte zwischen zwei Atomen

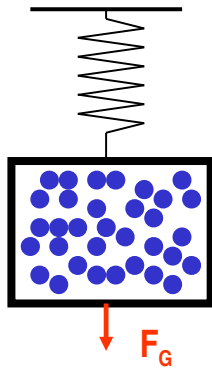


Chemische Bindung

$$F_{\text{chem}} = 1\text{eV} / 0.1\text{ nm}$$

1.6 nN

„Kräfte Spüren“



1 nm³ Wasser (33 Moleküle)

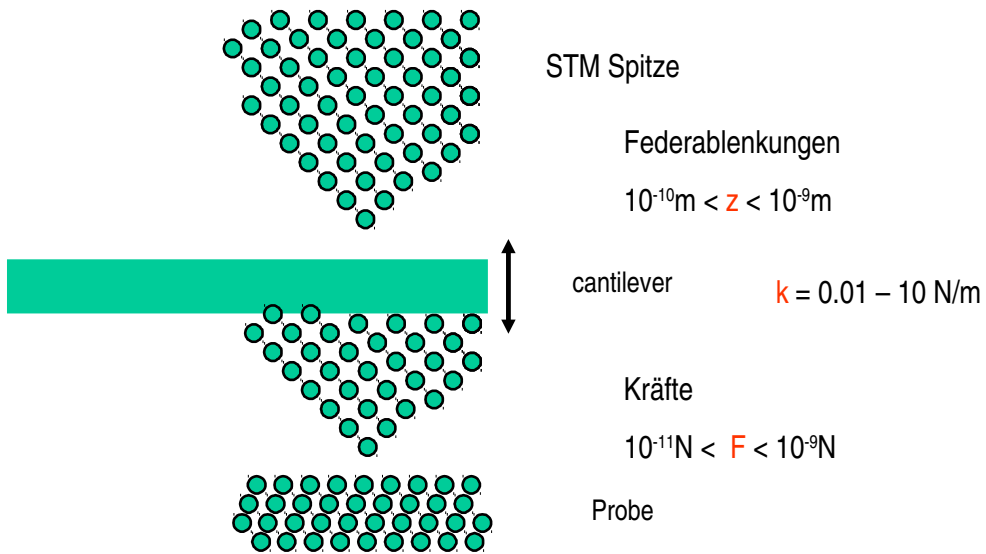
$$F_G = 10^{-23}\text{ N} = 10^{-14}\text{ nN}$$



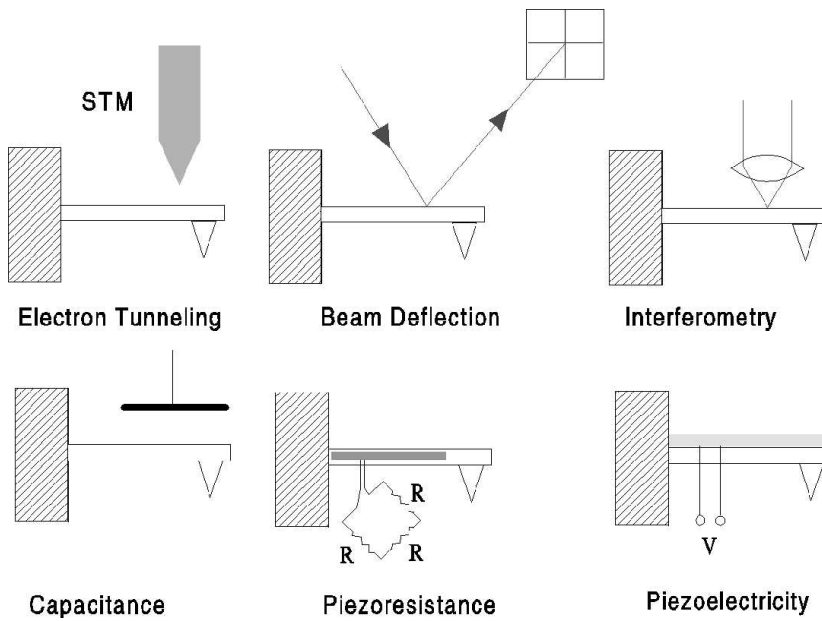
0.01 g

$$F = 0.1\text{ mN} = 10^5\text{ nN}$$

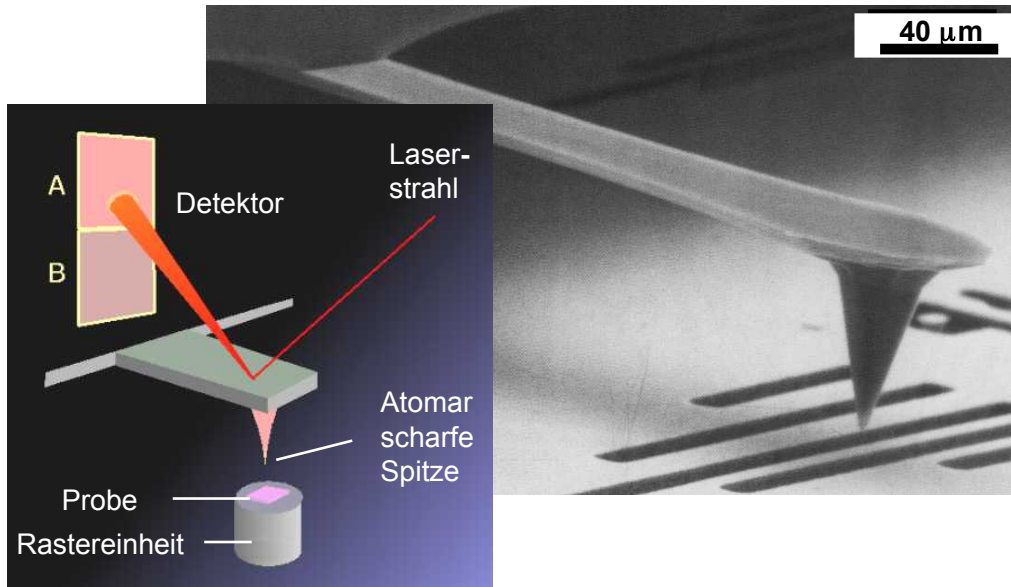
Prinzip des ersten AFMs



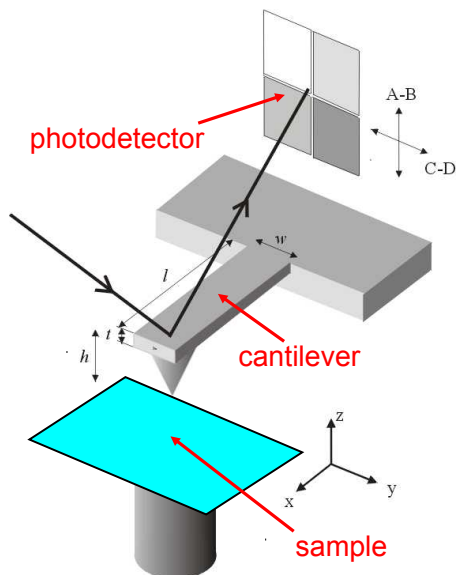
Ablenkungssensoren



„Beam deflection“-Methode

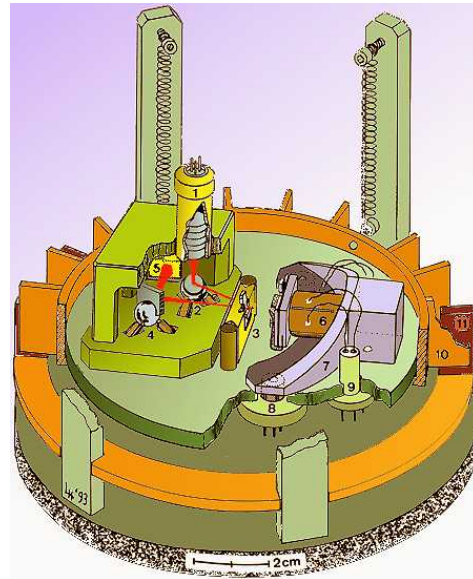


Atomic Force Microscopy (beam deflection)

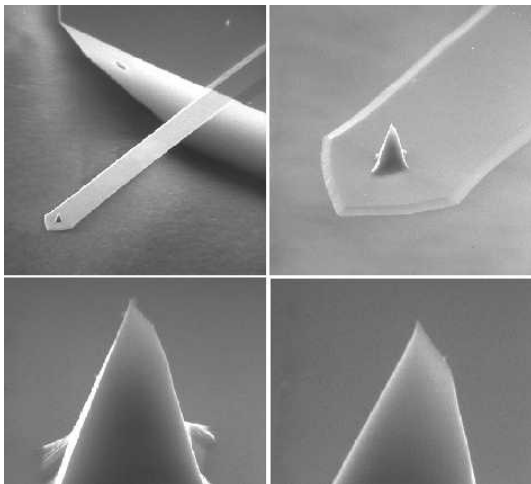


- The normal and lateral forces on a sharp tip sliding on a surface are sensed using a laser beam
- Forces < 1 nN can be measured

Beispiele



Microfabrizierte "Cantilever"



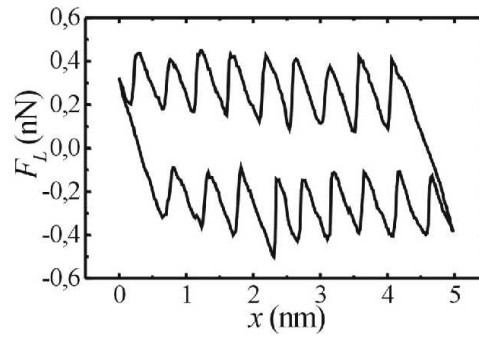
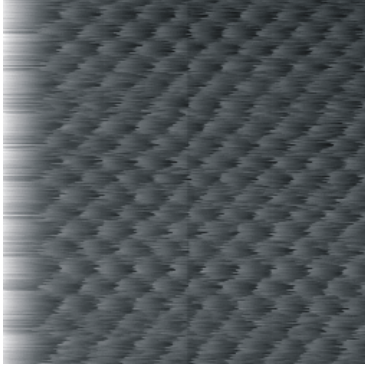
Länge : $l = 450 \mu\text{m}$
 Breite : $w = 45 \mu\text{m}$
 Dicke : $t = 1.5 \mu\text{m}$
 $E = 1.69 \cdot 10^{11} \text{ N/m}^2$

Spitzenhöhe: $12 \mu\text{m}$
 Spitzenradius: 10 nm

Federkonstante k :

$$k = \frac{Ewt^3}{4l^3} = 0.15 \text{ N/m}$$

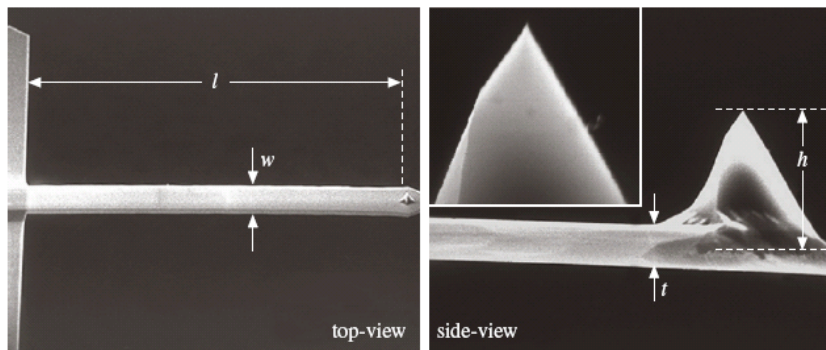
Atomic stick-slip



(friction map and friction loop on NaCl(100) in UHV)

Force Calibration

- Simple if **rectangular** cantilevers are used
- Cantilever width, thickness and length, tip height: from **SEM pictures**



Force Calibration

- Cantilever **thickness** also from the **resonance frequency**:

$$t = \frac{2\sqrt{12}\pi}{1.875^2} \sqrt{\frac{\rho}{E}} f_0 l^2$$

- ρ , E : density and Young modulus
(Nonnenmacher et al., JVSTB 1991)
- For pure silicon:

$$\rho = 2.33 \cdot 10^3 \text{ kg/m}^3$$

$$E = 1.69 \cdot 10^{11} \text{ N/m}^2$$

Force Calibration

- **Normal** and **lateral spring constants** of cantilever:

$$c_N = \frac{Ewt^3}{4l^3} \quad c_L = \frac{Gwt^3}{3h^2l}$$

- G : shear modulus
- For pure silicon:

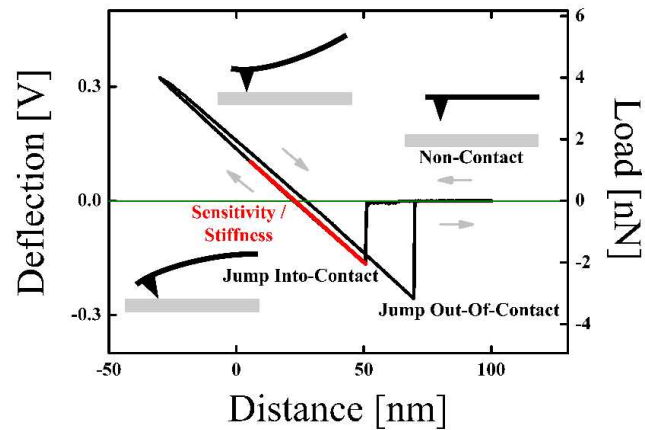
$$\rho = 2.33 \cdot 10^3 \text{ kg/m}^3$$

$$E = 1.69 \cdot 10^{11} \text{ N/m}^2$$

$$G = 0.5 \cdot 10^{11} \text{ N/m}^2$$

Force Calibration

- Next step: **sensitivity of photodetector**
- Force-distance curves on hard surfaces (e.g. Al_2O_3):



- Scanner movement = cantilever deflection
- Slope \rightarrow sensitivity

Force Calibration

- **Normal and lateral forces:**

$$F_N = c_N S_z V_N \quad F_L = \frac{3}{2} c_L \frac{h}{l} S_z V_L$$

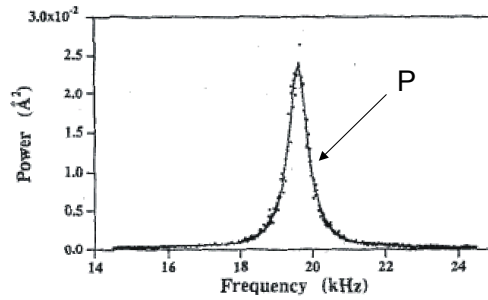
(if the laser beam is above the probing tip!)

- V_N, V_L : normal and lateral signals

Force Calibration

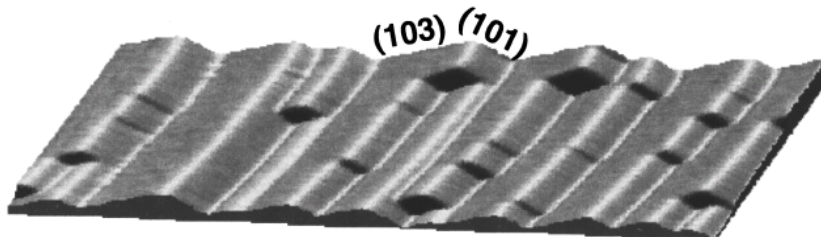
- Alternative method: Spring constant **from thermal power spectrum** (Hutter et al., RSI 1993)
- Correct relation (Butt et al., Nanotech. 1995):

$$c_N = \frac{4k_B T}{3P}$$

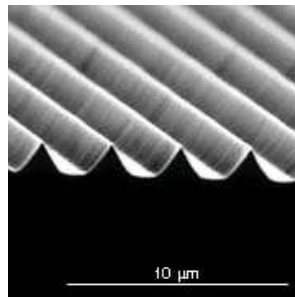


Force Calibration

- Alternative method: Scanning over profiles with **well-defined slope** (Ogletree et al., RSI 1996)



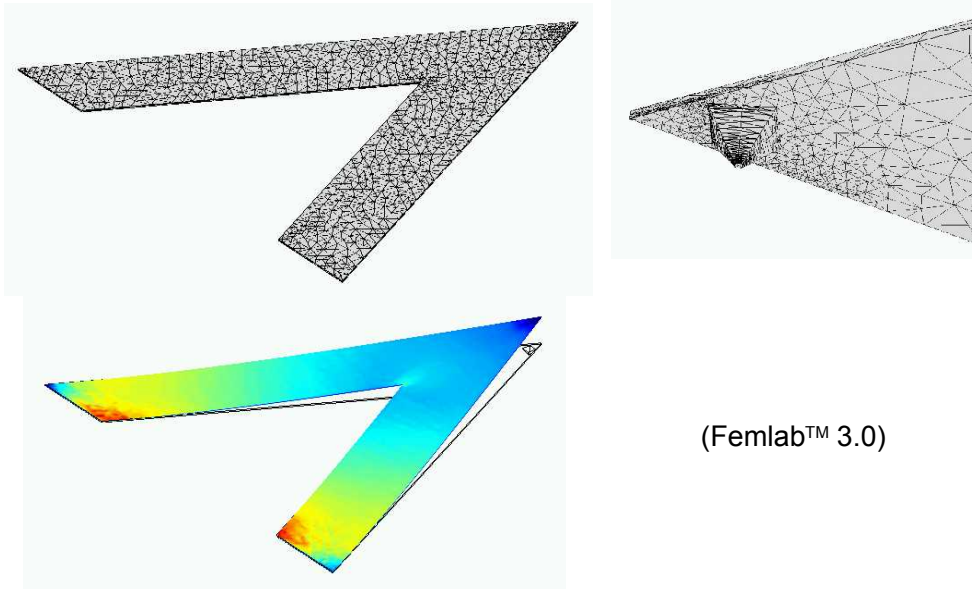
Commercially available grating:



(TGG01, NT-MDT,
Moscow)

Force Calibration

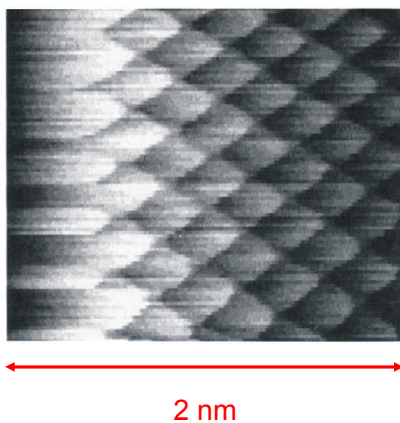
- Different shapes → Finite elements analysis



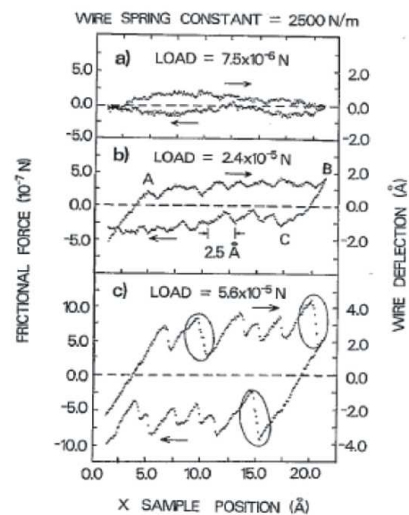
(Femlab™ 3.0)

Atomic-Scale Measurements

- Atomic friction on graphite:



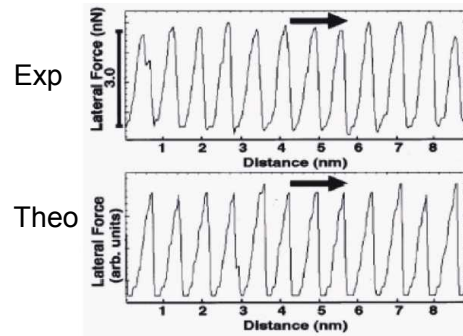
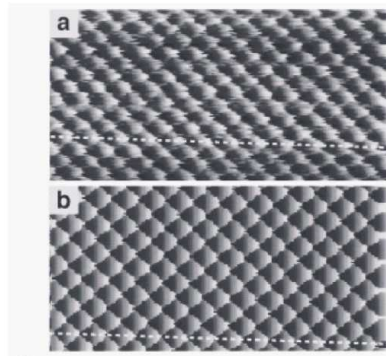
(Mate at al., PRL 1987)



Atomic-Scale Measurements

- Friction on **insulating surfaces** (Lüthi et al., JVSTB 1996):

KBr

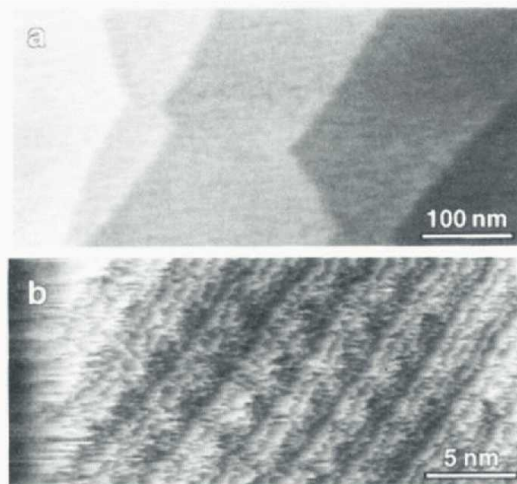


- No individual defects are observed

Atomic-Scale Measurements

- Friction on **semiconductors** (Howald et al., PRB 1995):

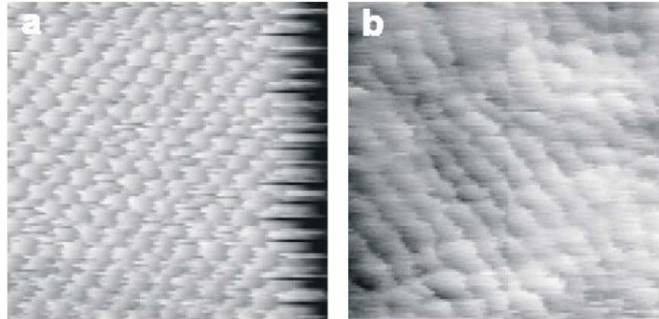
Si(111)7x7



(tip coated with PTFE)

Atomic-Scale Measurements

- Friction on **metal surfaces** (Bennewitz et al., Trib. Lett. 2001):



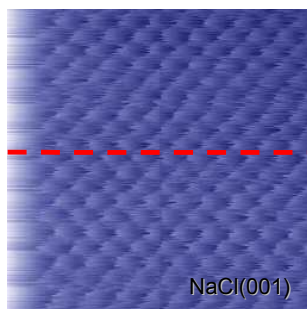
Cu(111)

Cu(100)

Irregular features on the (100) surface (less packed!)

Atomic friction on crystal surfaces

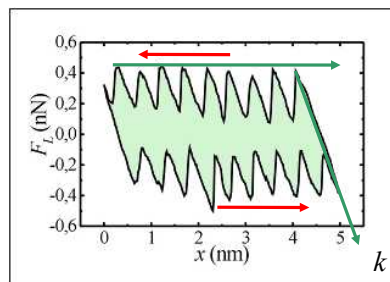
Our model systems: alkali halide surfaces (easy preparation, simple structure)



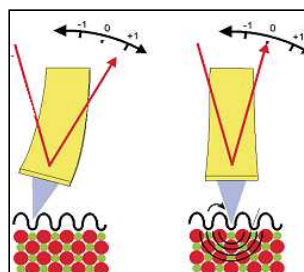
NaCl(001)

5 nm

Tomlinson model:
(Phyl. Mag. 1929)



$$F_L^{\max} = \frac{2\pi V_0}{a}$$

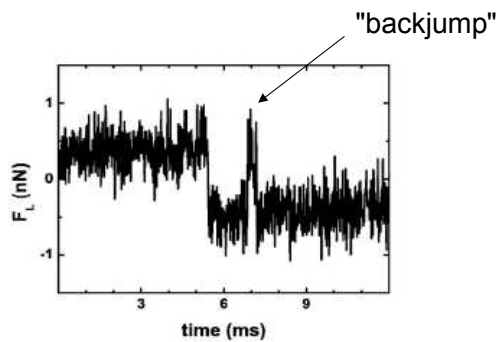
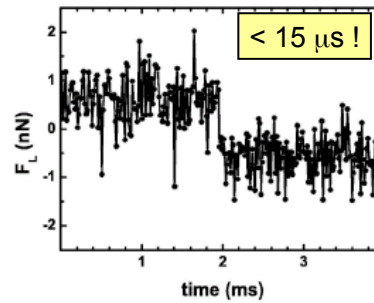
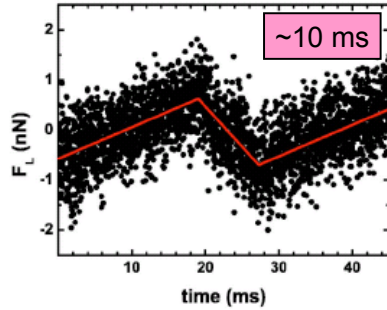


$$V_0 \sim 1 \text{ eV}$$

$$k \sim 1 \text{ N/m}$$

Atomic-Scale Measurements

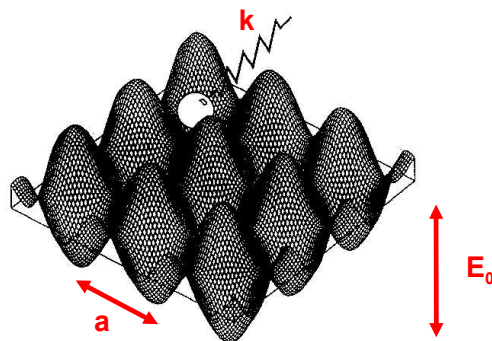
- Wide distribution of slip durations:



Why?

Modelling Atomic Friction

- The tip is subject to
 - 1) periodic interaction with the underlying surface
 - 2) elastic deformation of the cantilever



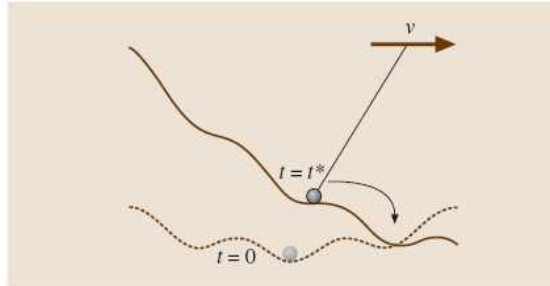
- In 1D the corresponding potential energies are represented by

- 1) a sinusoid
- 2) a parabola

Modelling Atomic Friction

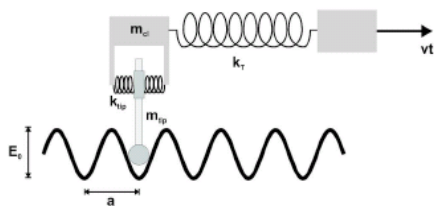
- Total energy of the system:

$$U_{\text{tot}}(x,t) = -\frac{E_0}{2} \cos \frac{2\pi x}{a} + \frac{1}{2} k_{\text{eff}} (vt - x)^2$$



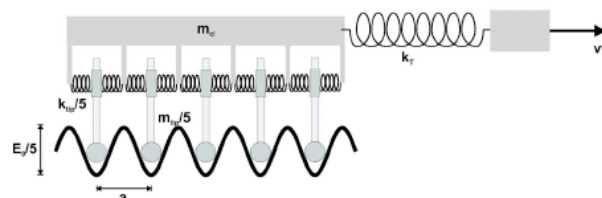
- The tip can "stick" to the minima of the potential profile

Modelling Atomic Friction



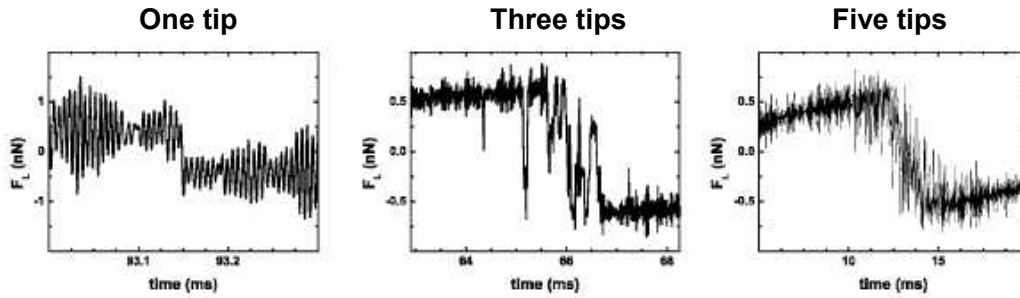
single contact

multiple contact



Modelling Atomic Friction

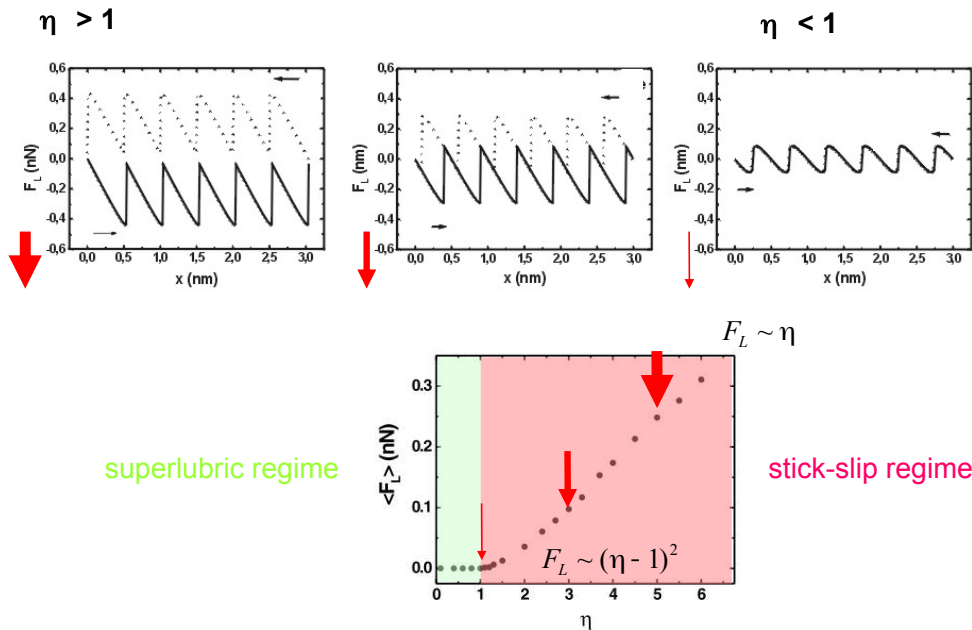
- Tip → Langevin equation (including thermal noise)
- Cantilever → Newton equation (without thermal noise)



- Long slip times are found with multiple tips only
(Maier et al., PRB 2005)

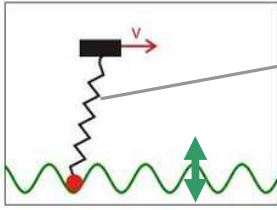
Superlubricity

- From the Tomlinson model (without thermal activation):



“Dynamic superlubricity”

A third way to reduce friction: Tomlinson model with TIME modulation

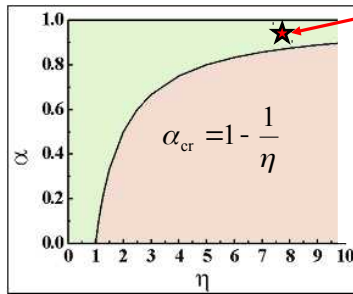


$$V_{\text{elas}} = \frac{k\alpha^2}{2}$$

$$V_{\text{int}} = V_0 \cos \frac{2\pi x}{a}$$

$$\eta = \frac{(2\pi)^2 V_0}{ka^2}$$

Phase-diagram in the η - α plane:



High loads can be applied!

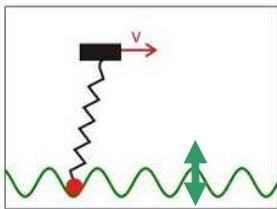
$$V_0 \rightarrow V_0(1 + \alpha \cos \omega t)$$

$$\eta_{\text{eff}} = \eta(1 - \alpha)$$

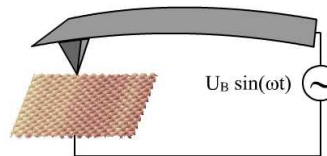
E. Gnecco et al., J. Phys.: Condens. Matt. a20 (2008) 354004

“Dynamic superlubricity”

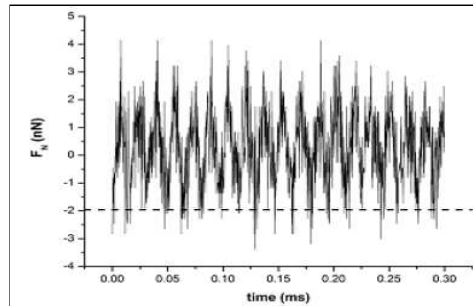
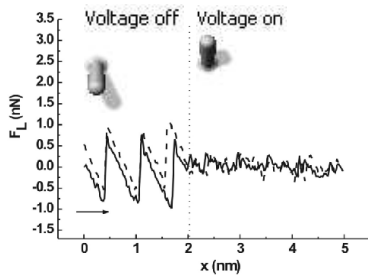
A third way to reduce friction: Tomlinson model with TIME modulation



AC actuation of the nanocontact:

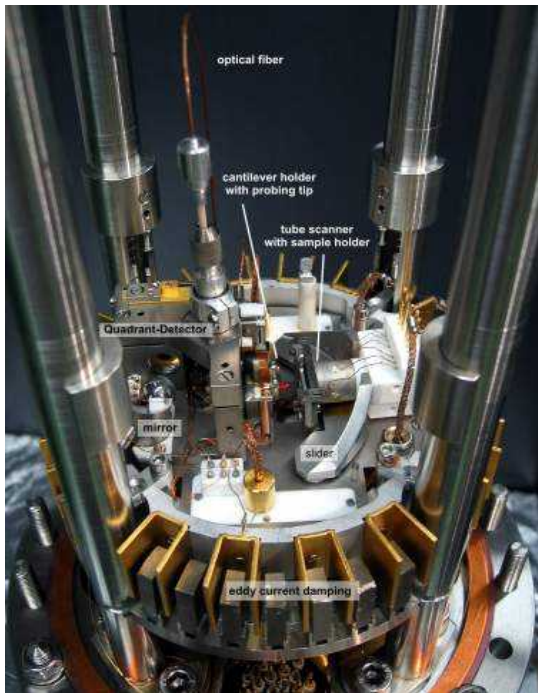


NaCl(001)



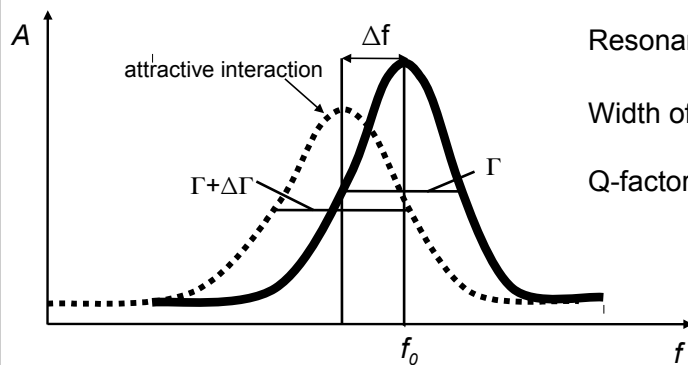
A. Socoliuc et al., Science 313 (2006) 207

Noncontact-AFM (nc-AFM)



- UHV: Base pressure below 1×10^{-10} mbar
- Operation at room temperature
- Mixed mode: AFM/STM
- Beam deflection method
- Bandwidth of the photodetector: 3MHz
- Evaporation of molecules from a k-cell kept at 165°C or 170°C

Quantitative understanding of nc-AFM



Resonance frequency: f_0

Width of resonance curve (FWHM): Γ

Q-factor: $Q = \frac{2\pi \cdot f_0}{\Gamma}$

Conservative forces \Rightarrow shift of resonance curve Δf

Dissipative forces \Rightarrow broadening of curve $\Delta\Gamma$

Forces in nc-AFM

Frequency modulation: $f_0 = \frac{1}{2\pi} \sqrt{\frac{k}{m^*}}$ $\Delta f = -\frac{f_0}{2k} \frac{\partial F_{tot}}{\partial z}$

⇒ measured topography = surface of constant $\frac{\partial F}{\partial z}$

$$F_{tot} = F_{chem} + F_{mag} + F_{el} + F_{vdW}$$

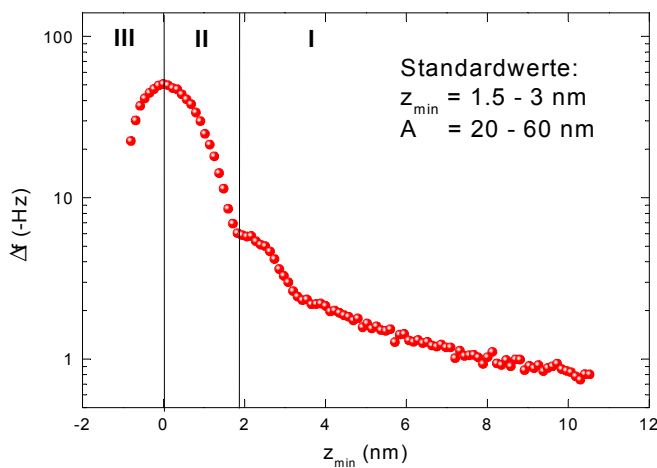
bonding between
tip and sample
atoms
(only for $d < 5 \text{ \AA}$)

only for
magnetically
sensitive tips

$$F_{el} = -\frac{1}{2} \frac{\partial C}{\partial z} V^2$$

$$F_{vdW} = -\frac{HR}{6d^2}$$

Dynamic Mode, non-contact

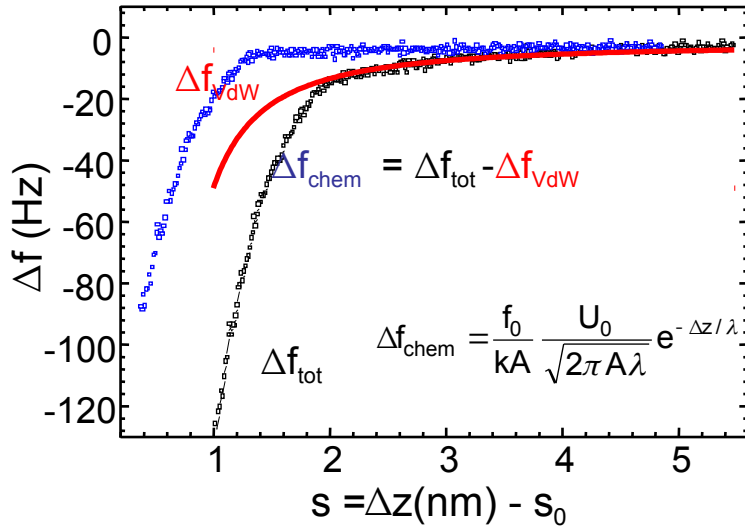


region I:
attractive forces
non-contact mode

region II:
attractive forces
atomic resolution

region III:
repulsive forces
tapping mode

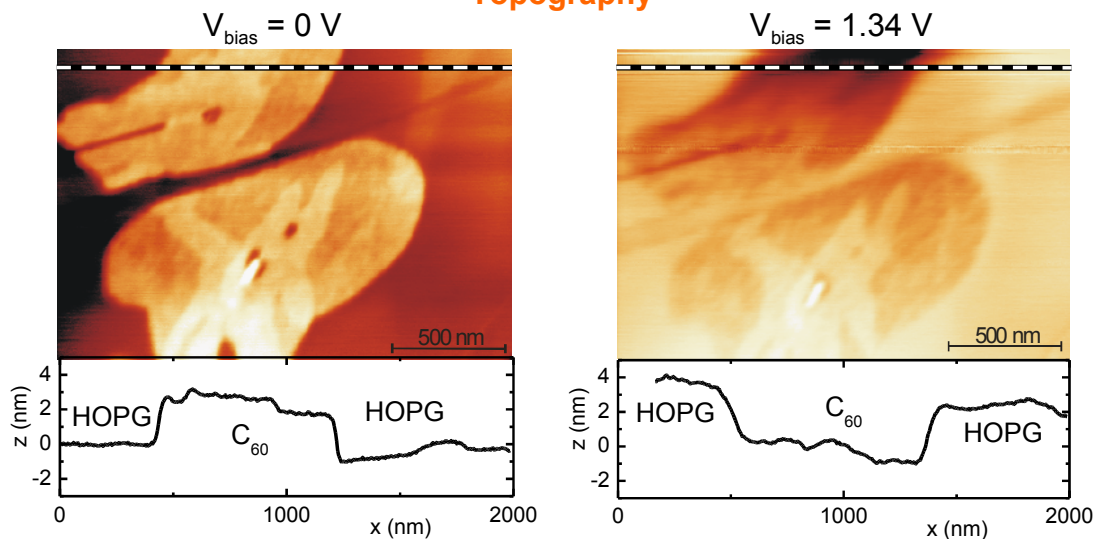
Short range interaction



$\lambda = 0.35 \text{ nm}$
 $U_0 = -4.7 \text{ eV}$
 $s_0 = 0.45 \text{ nm}$

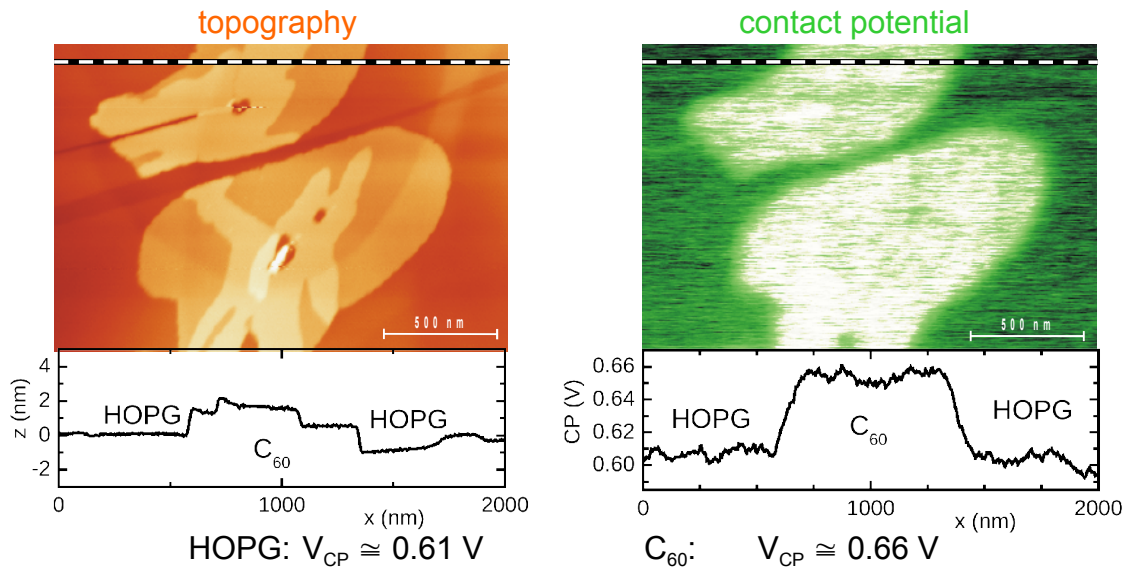
inhomogeneous sample: HOPG + 1/2 monolayer C₆₀

Topography



→ contrast inversal: HOPG ↔ C₆₀

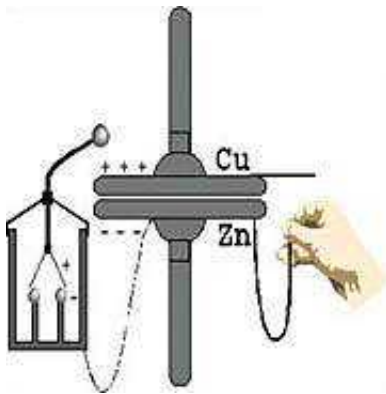
inhomogeneous sample: HOPG + 1/2 monolayer C60



⇒ NC-AFM: residual electrostatic force for fixed V_{bias}

Makroskopische Kelvin-Sonde

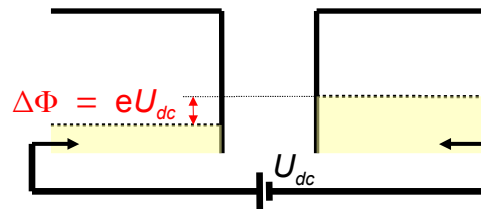
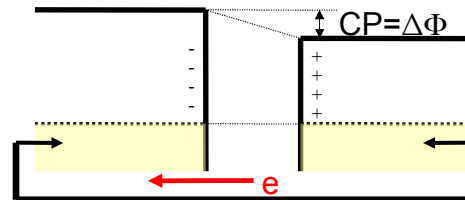
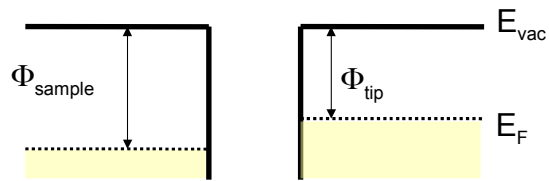
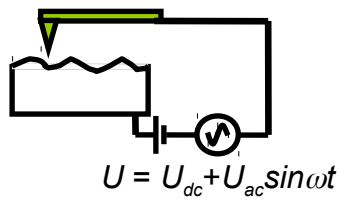
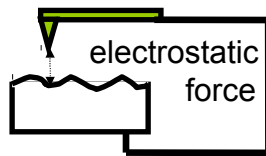
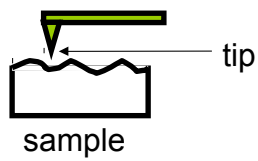
Lord Kelvin 1861



Verschiebestrom

$$I(t) = (U_{dc} - U_{CPD}) f \Delta C \cos \omega t.$$

Kelvin Principle



Electrostatic Forces in nc-AFM

$$F_{el} = -\frac{1}{2} \frac{\partial C}{\partial z} V_{eff}^2 \quad \Rightarrow \quad F_{el} = -\frac{1}{2} \frac{\partial C}{\partial z} (V_{bias} - V_{CP})^2$$

$$V_{CP} = 1/e \cdot (\Phi_{tip} - \Phi_{sample})$$

contact potential
Φ - work function

apply bias:

$$V_{bias} = V_{dc} + V_{ac} \cdot \sin(\omega t)$$

Kelvin Probe Force Microscopy

$$F_{el} = -\frac{1}{2} \frac{\partial C}{\partial z} V_{eff}^2 = F_{dc} + F_{\omega} + F_{2\omega}$$

$$F_{dc} = -\frac{\partial C}{\partial z} \frac{1}{2} (V_{dc} - V_{CP})^2 + \frac{V_{ac}^2}{4}$$

$$F_{\omega} = -\frac{\partial C}{\partial z} (V_{dc} - V_{CP}) V_{ac} \sin(\omega t)$$

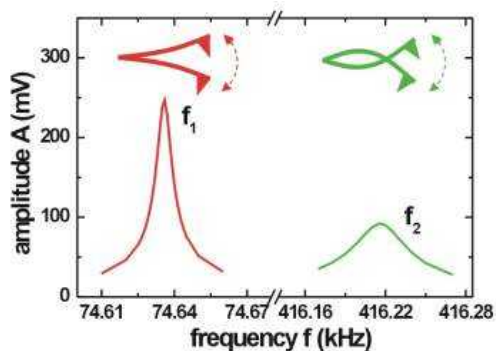
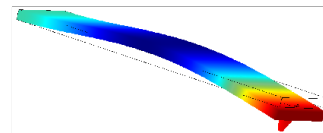
$$F_{2\omega} = \frac{\partial C}{\partial z} \frac{V_{ac}^2}{4} \cos(2\omega t)$$

AM-KPFM
Amplitude Modulation

FM-KPFM
Frequency Modulation

AM – KPFM Amplitude Modulation Detection

$$F_{\omega} = -\frac{\partial C}{\partial z} (V_{dc} - V_{CP}) V_{ac} \sin(\omega t)$$

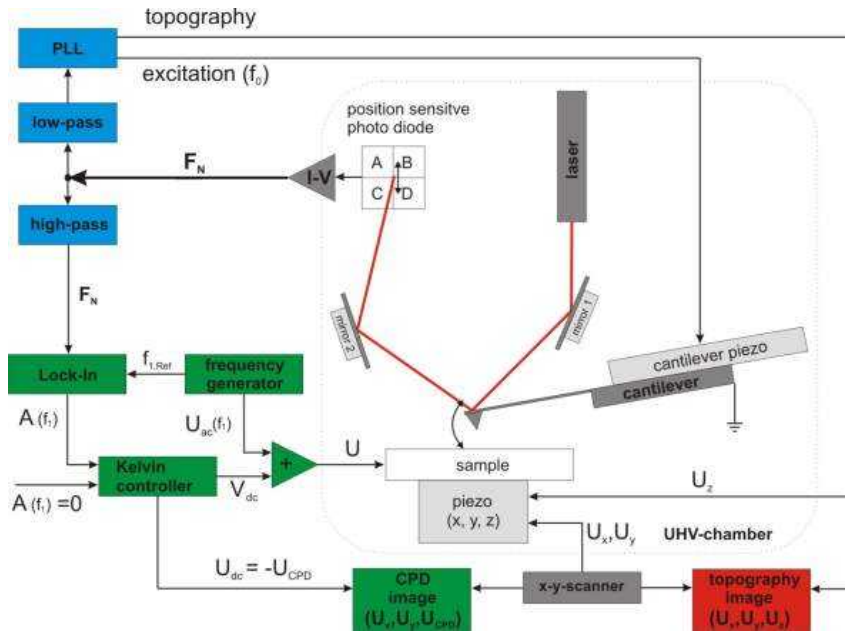


- tune ω to the second resonance f_2
- detection of the oscillation amplitude A_{ω} with a lock-in
- limiting factor: bandwidth of the photodiode

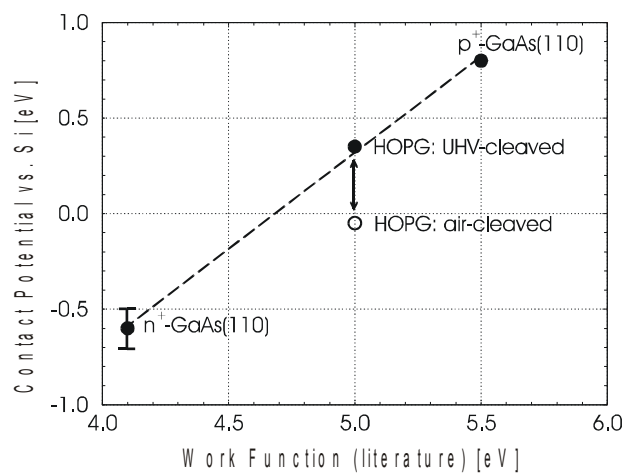
$$A_{\omega} \propto F_{\omega}$$



Experimental Setup nc-AFM & AM-KPFM



KPFM calibration and absolute work function



Φ -Si-Cantilever = 4.70 (± 0.1) eV

$U_{ac} = 100$ mV

→ absolute and quantitative work function determination

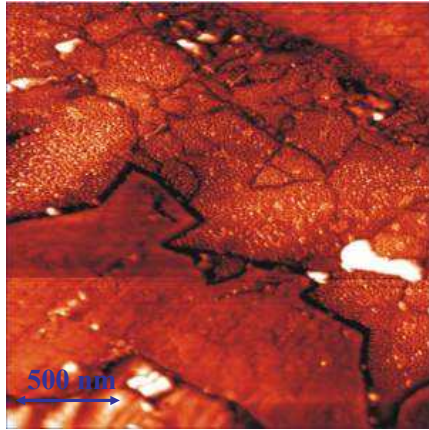
Polished Cross Section of a CuGaSe₂ Solar Cell

CuGaSe₂ solar cell device: $V_{oc} = 820 \text{ mV}$, $\eta = 4.6 \%$

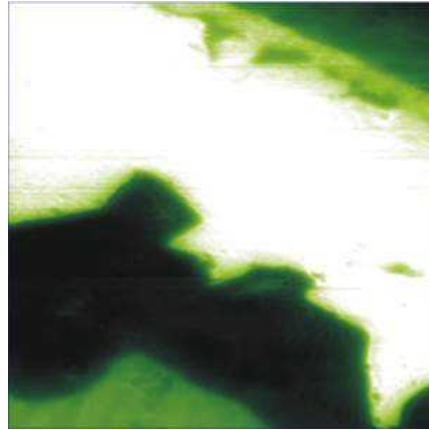
polished and Ar-ion sputtered cross section

topography

work function



$\Delta z = 65 \text{ nm}$



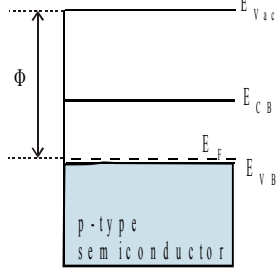
Mo,
 $\Phi=4.20\text{eV}$
MoSe₂,
 $\Phi=4.40\text{eV}$
CuGaSe₂,
 $\Phi=4.80\text{eV}$

n-ZnO:Ga,
 $\Phi=4.0\text{eV}$

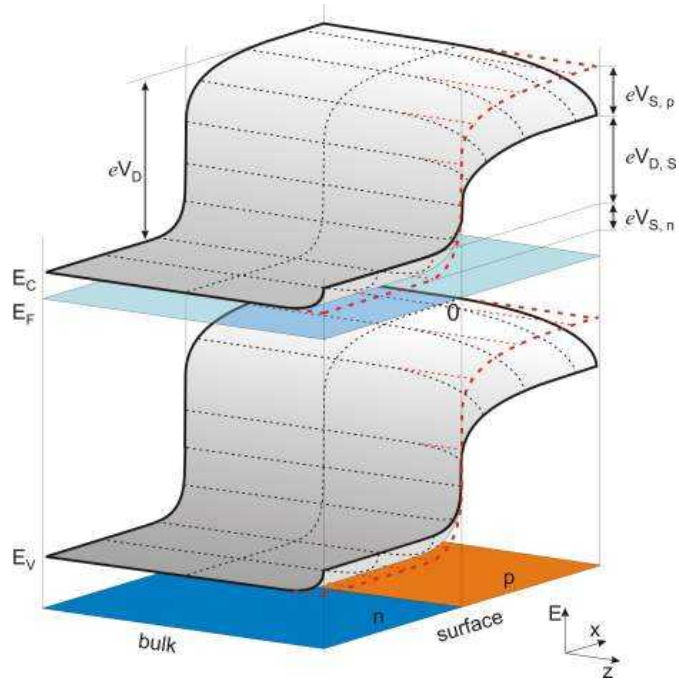
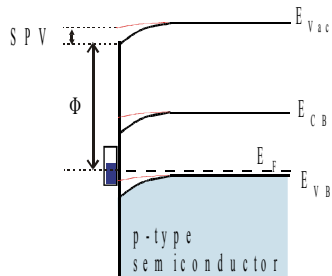
Glatzel *et al.*, APL **81**, 2017 (2002)

Surface Effects

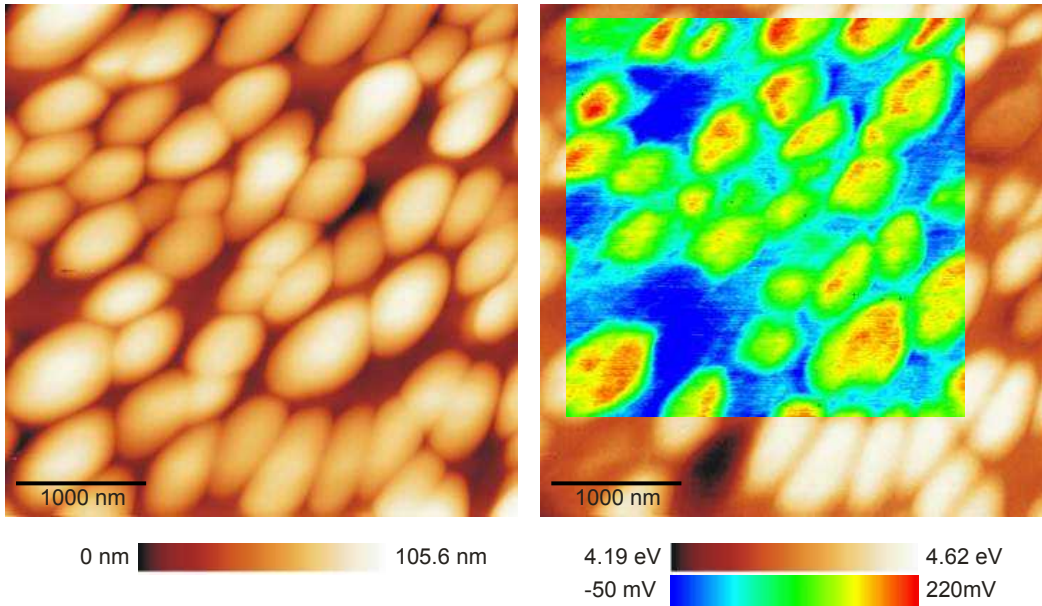
no surface states



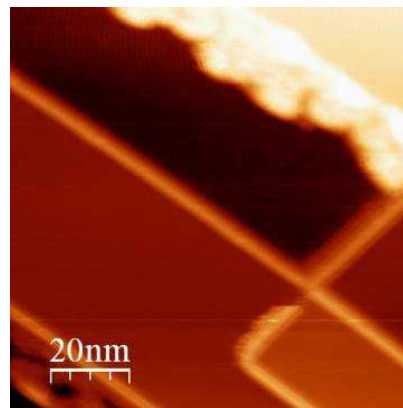
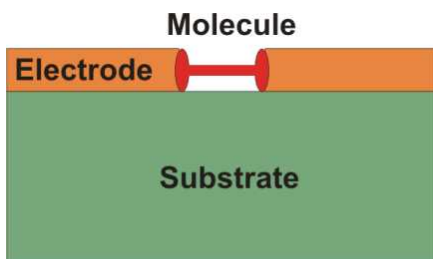
surface states



Surface Photovoltage MDMO-PPV/PCBM – 675nm



Motivation Molecular electronics

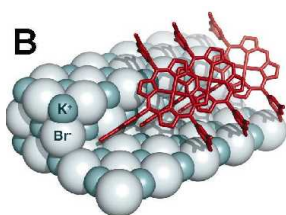


Molecules on Insulators:

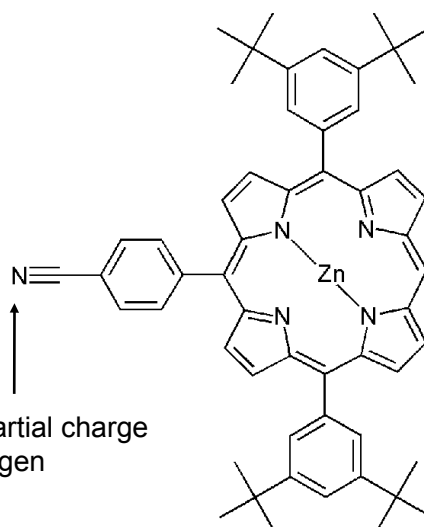
- No STM possible – nc-AFM mandatory
- Low diffusion barrier but high intermolecular interaction
- Low temperatures – easier to “fix” molecules but not so easy to find applications

Asymmetric Cyano-Porphyrins

Natural light harvesting complexes



S. Meier et al., *Small*, 2008, 4, 1115

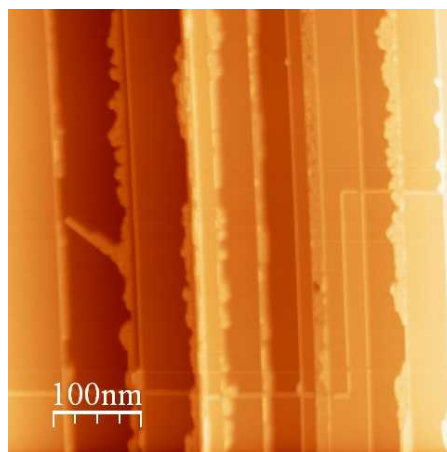


Balaban et al., *Acc. Chem. Res.* **2005**, 38, 612 – 623

Wire Formation

Decoration of step edges on KBr(100)

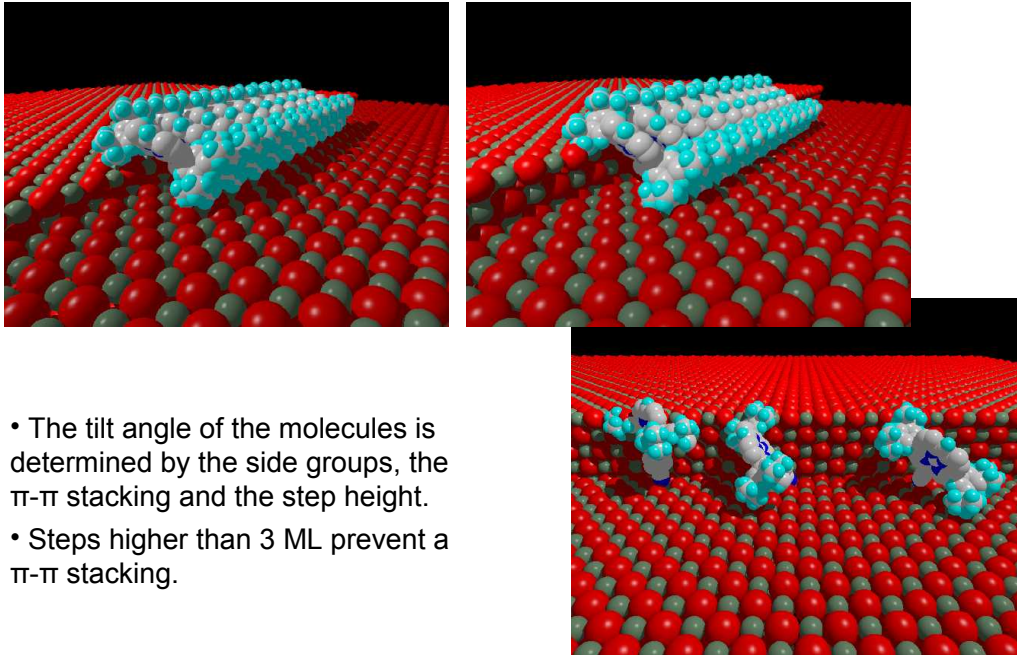
- In situ cleaved KBr with 0.5 ML of molecules
- Steps (< 1nm) are decorated with monowires
- Higher steps act as nucleation sites for structure growth across terraces



L. Zimmerli et al., *J. Phys.: Conf. Ser.*, 2007, 61, 1357

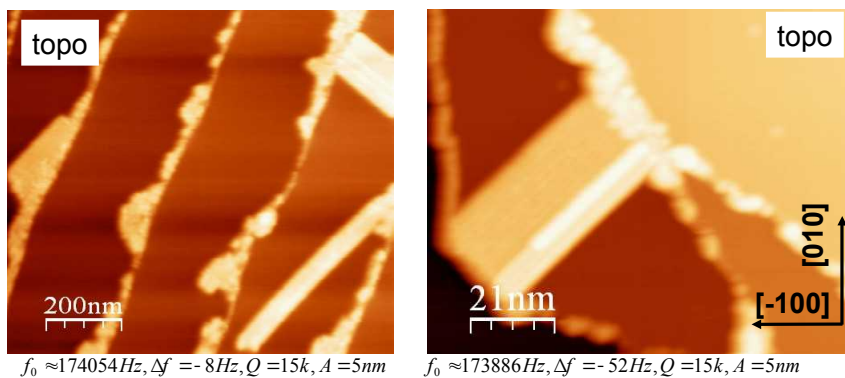
Wire Formation

Structural model



Molecular Assemblies

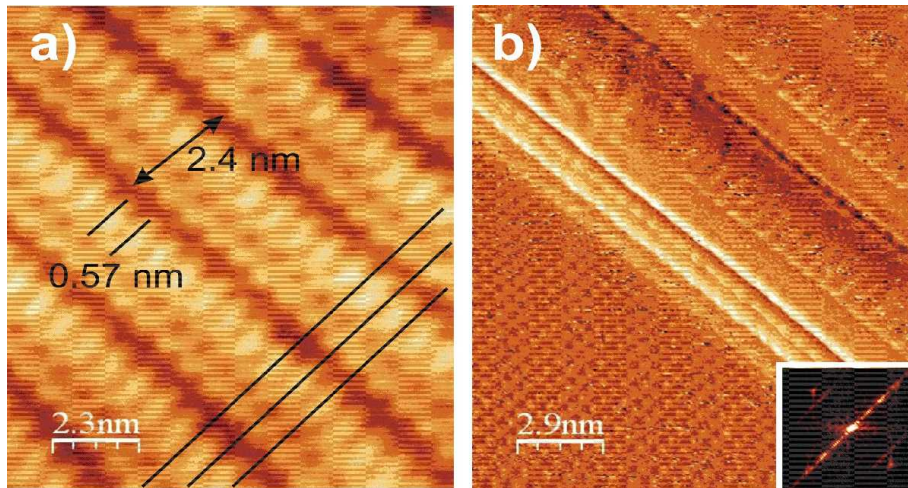
Multiwires on KBr



- Multiwire growth across terraces
- The $\langle 110 \rangle$ directions are clearly preferred
- Different heights are visible

Molecular Assemblies

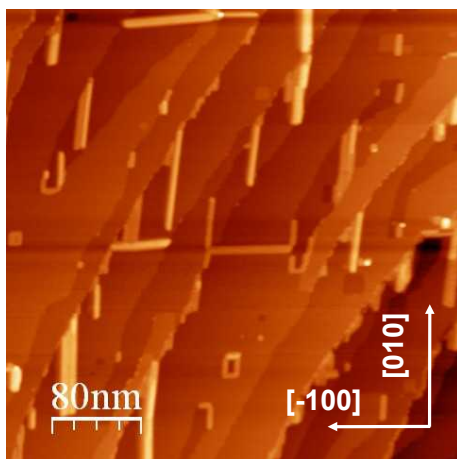
High resolution imaging



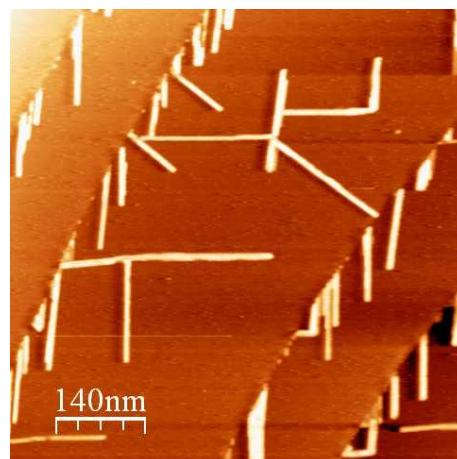
S. Meier et al., Small, 2008, 4, 1115

Molecular Assemblies

Molecular wires on NaCl



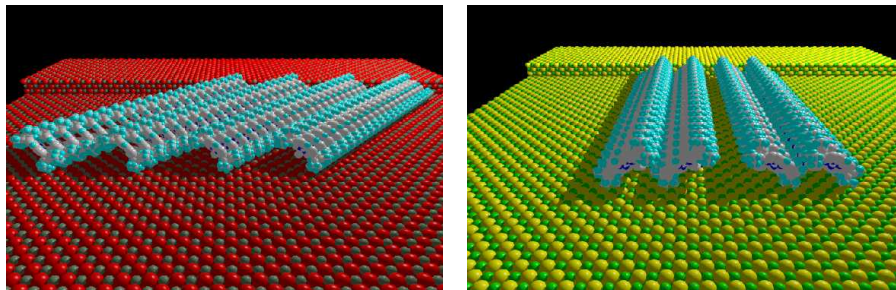
$f_0 \approx 170992 \text{ Hz}$, $\Delta f = -9.5 \text{ Hz}$, $Q = 15k$, $A = 40 \text{ nm}$



$f_0 \approx 170992 \text{ Hz}$, $\Delta f = -11 \text{ Hz}$, $Q = 15k$, $A = 40 \text{ nm}$

Molecular Assemblies

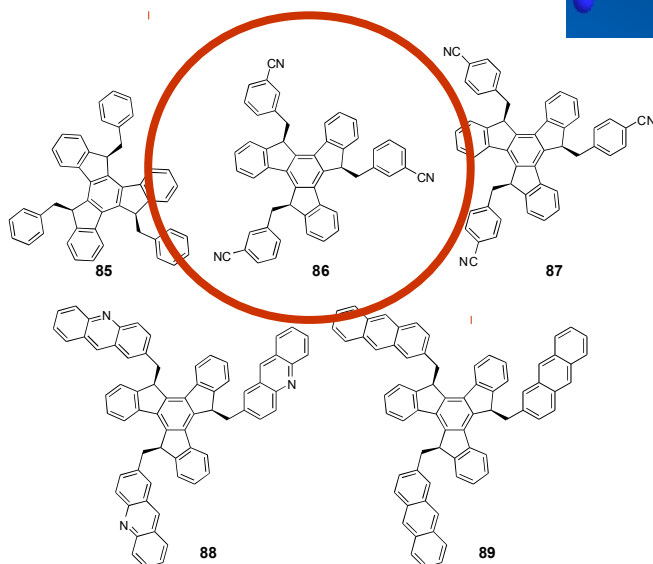
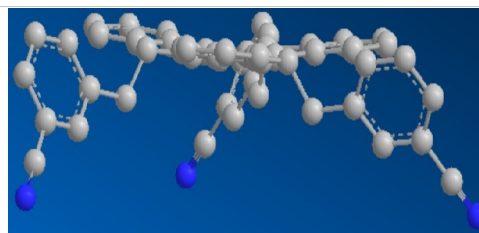
Structural model



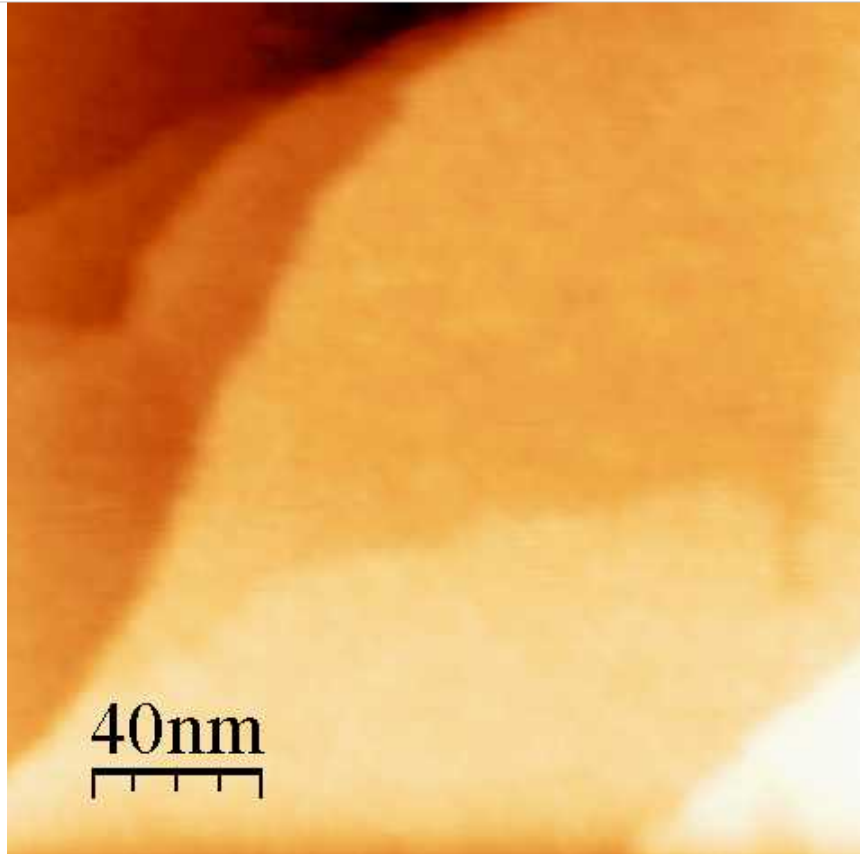
- Intermolecular equilibrium separation $\sim 5.7 \text{ \AA}$
- Directed growth by the substrate

Functionalized Truxenes

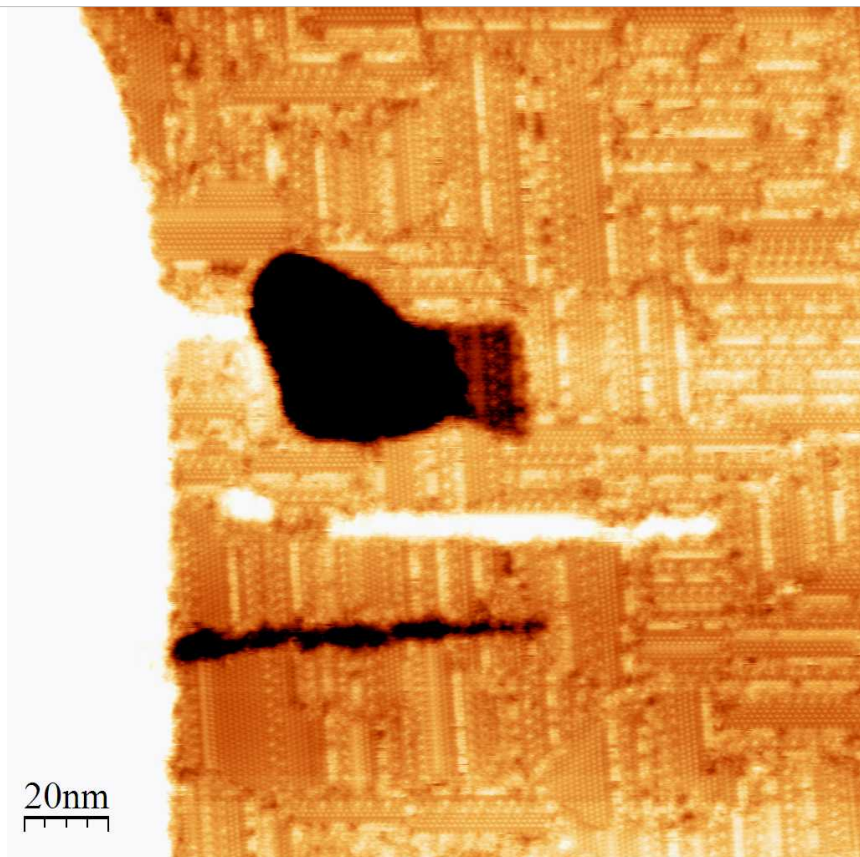
Structure



evaporation onto
the sample at RT

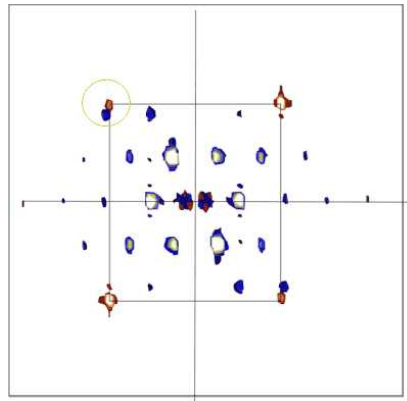
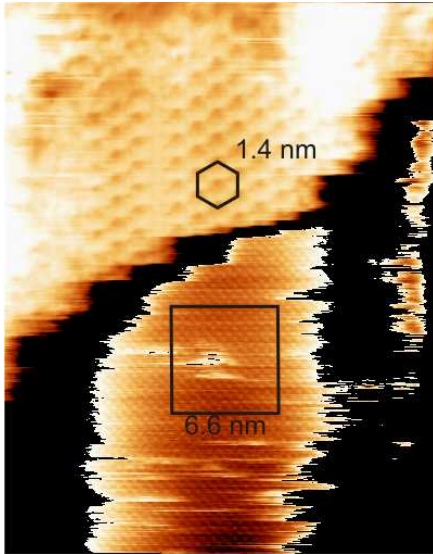


and the result of
post annealing at
155 C for 15 mins



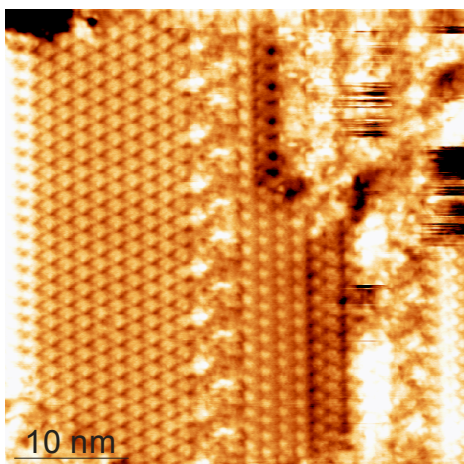
Truxene Self Assemblies

Hexagonal coordination on KBr

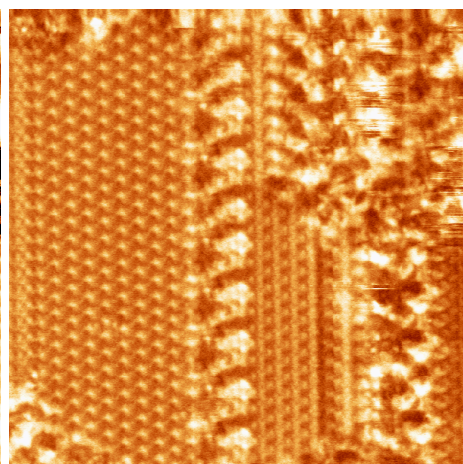


Truxene Self Assemblies

Various distinct structures



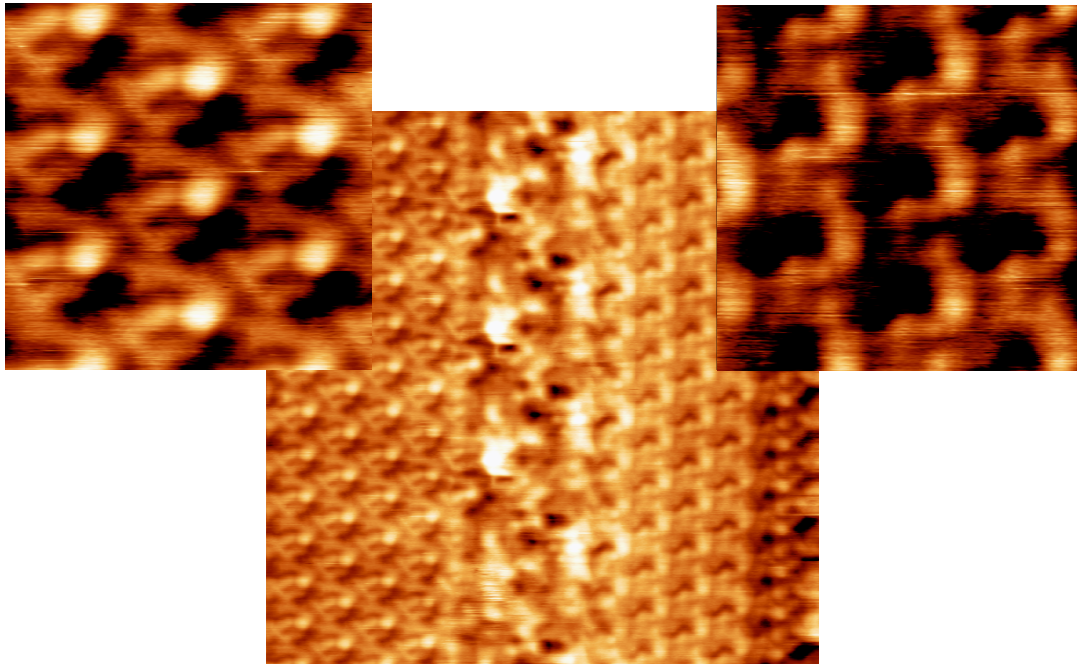
topography



dissipation

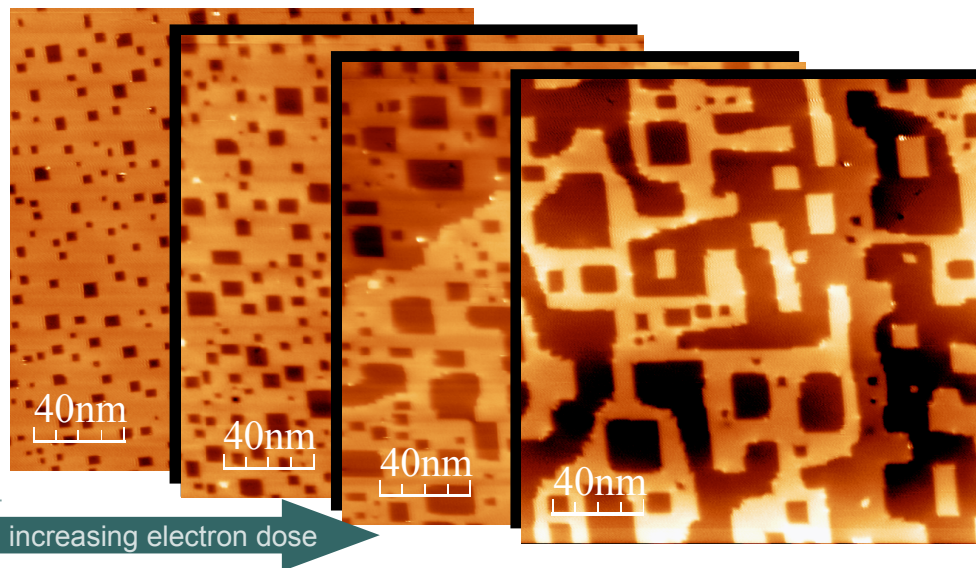
Truxene Self Assemblies

High resolution measurements



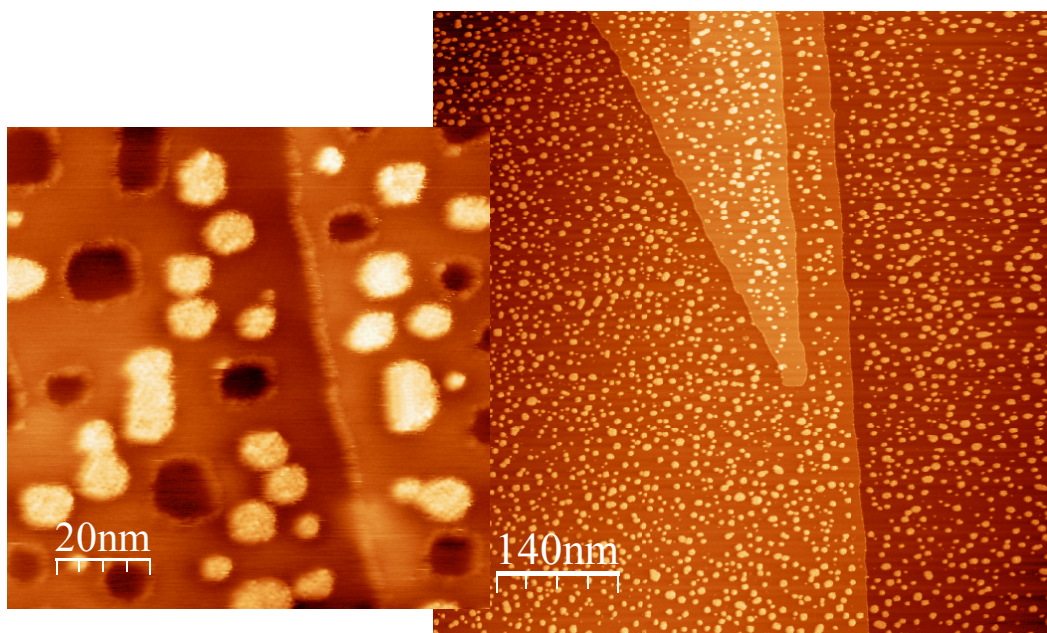
Single Crystal KBr

Substrate patterning by electron irradiation



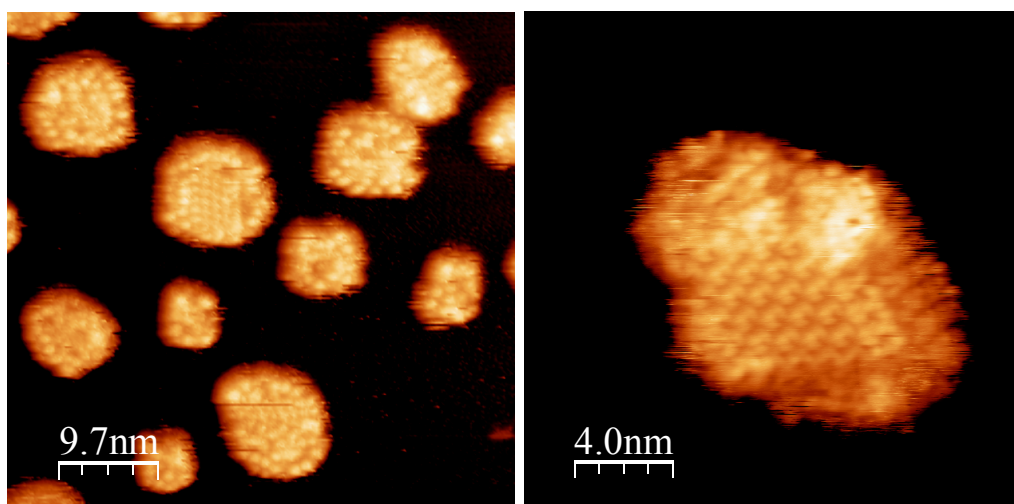
Truxenes on patterned surface

Filled and unfilled pits



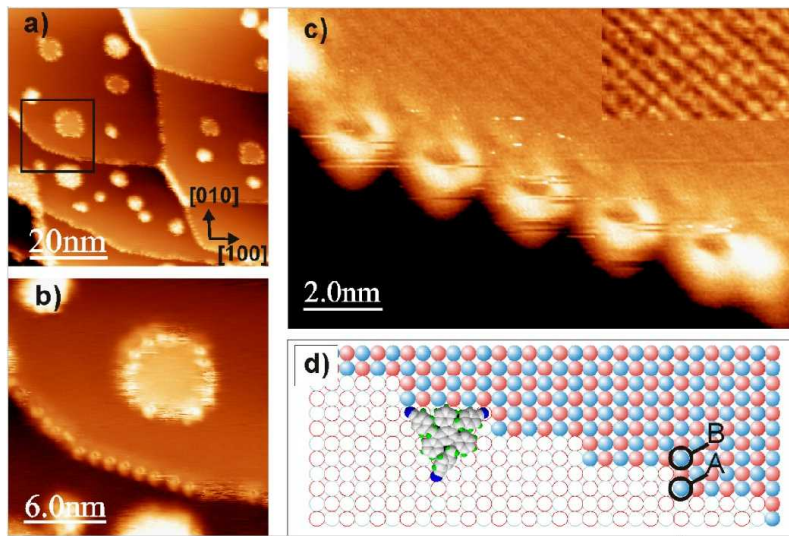
Truxenes on patterned surface

Organization within the pits



Imaging a Single Molecule

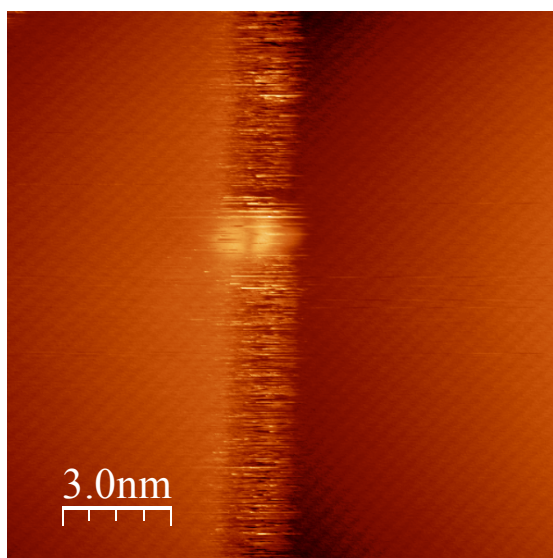
Measurements at RT



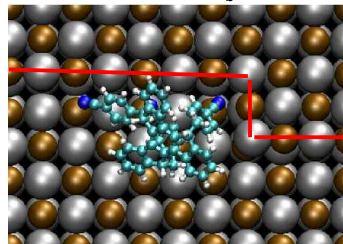
- Re-arrangement of the substrate, edges are running in the $[-3\ 1\ 0]$ direction
- no chemical interaction with the surface
- adsorbed on K or Br terminated double atomic kink

Imaging a Single Molecule

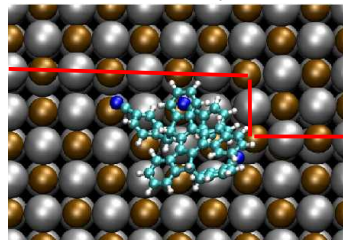
Measurements at RT



Br terminated, $E_b = 1.33\text{eV}$

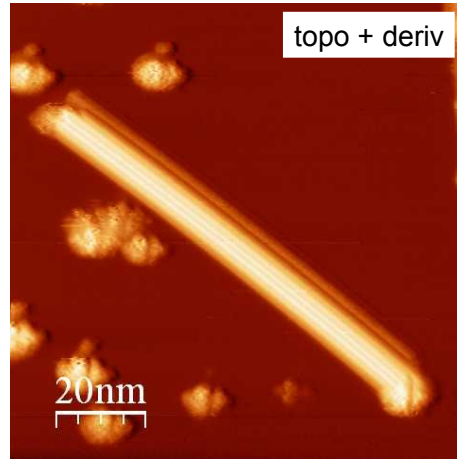
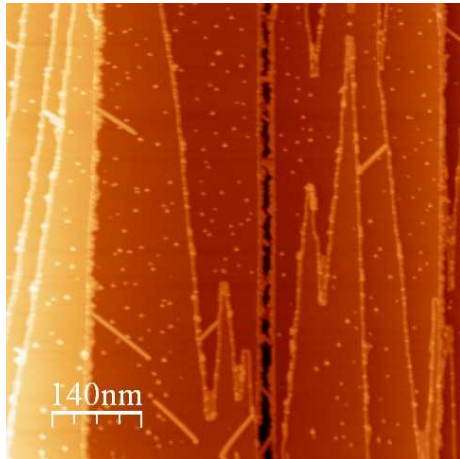
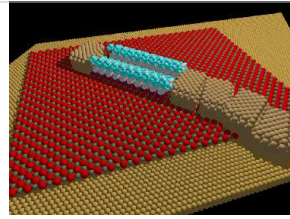


K terminated, $E_b = 1.17\text{eV}$



Contacting Molecular Assemblies

Au-Molecules-Au



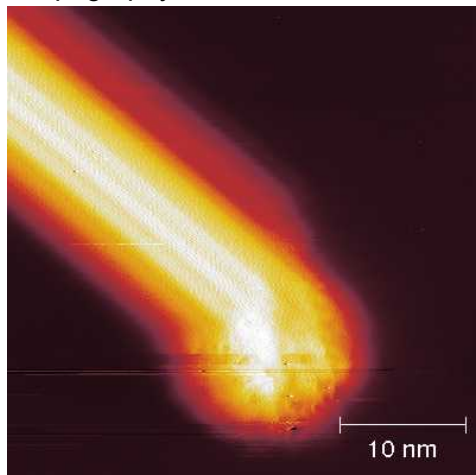
- Molecules arrange at steps and across terraces
- The growth is started/stopped at gold clusters.

Glatzel et al., Appl. Phys. Lett., 2009, 94, 063303

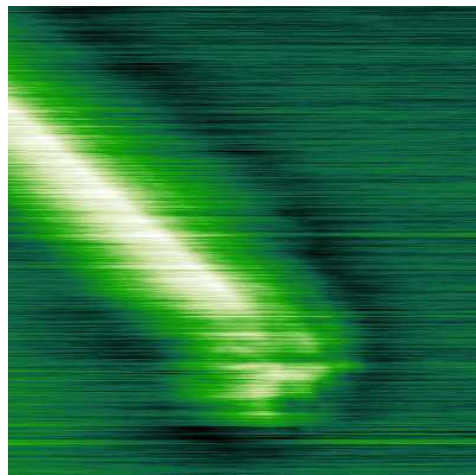
Contacting Molecular Assemblies

KPFM

Topography



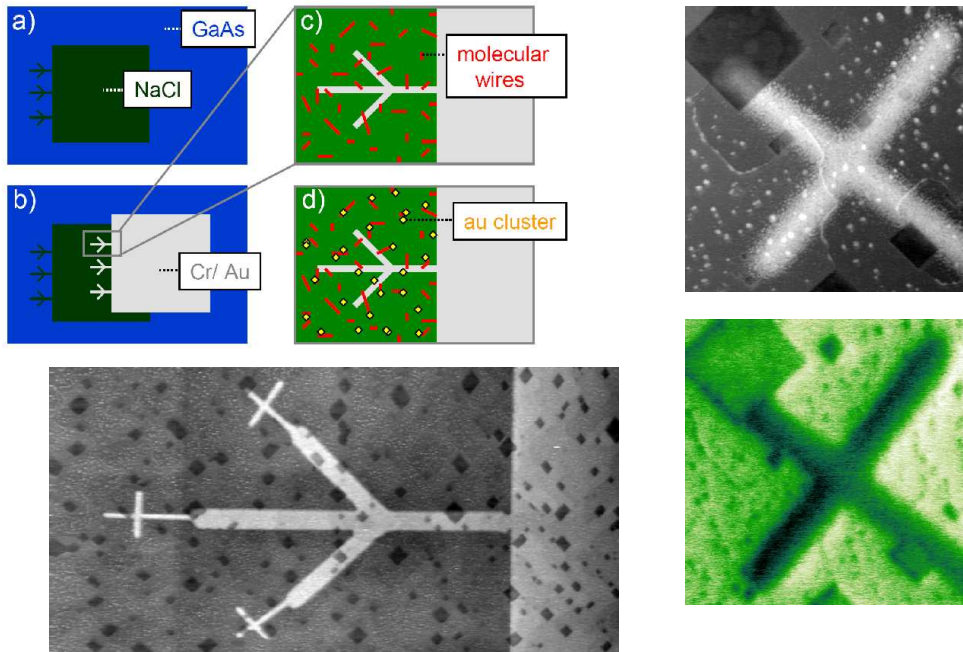
LCPD



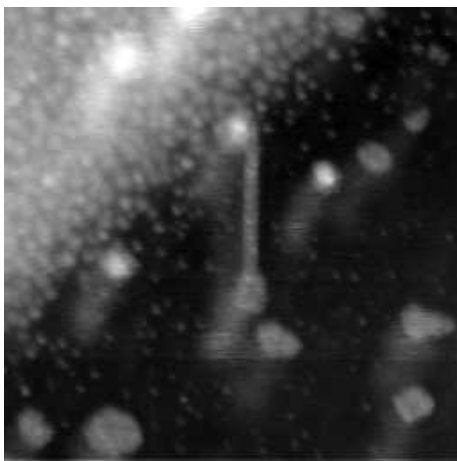
LCPD= -0.5...0.2eV

Glatzel et al., Appl. Phys. Lett., 2009, 94, 063303

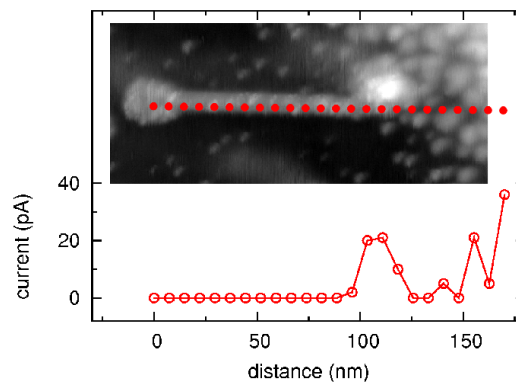
Contacting Molecular Assemblies Nanostencil (IBM Rüsçhlikon)



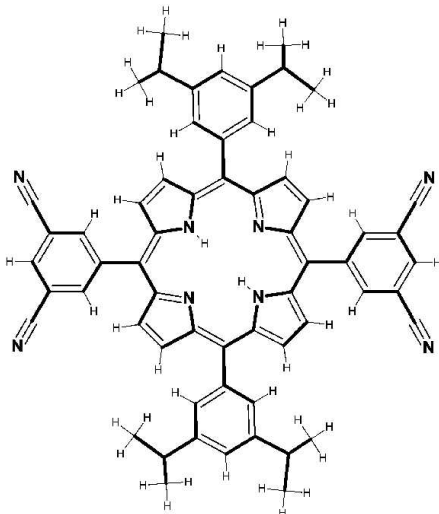
Contacting Molecular Assemblies Nanostencil (IBM Rüsçhlikon)



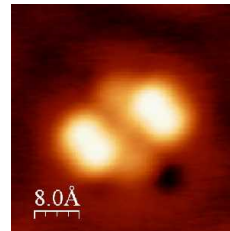
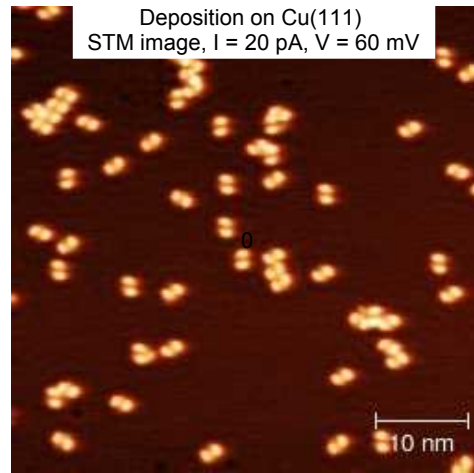
$300 \times 300 \text{ nm}^2$



Porphyrin with bicyanophenyl legs



2-bicyanophenyl, 2-aryl H₂-porphyrin synthesized by F. Diederich (ETH, Zurich)

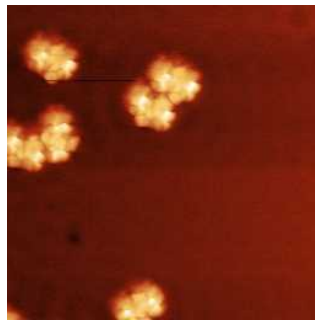
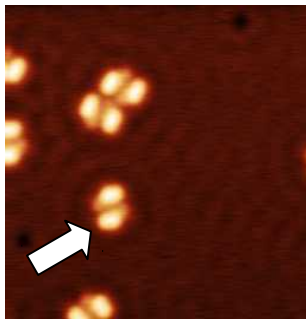


R. Pawlak et al.

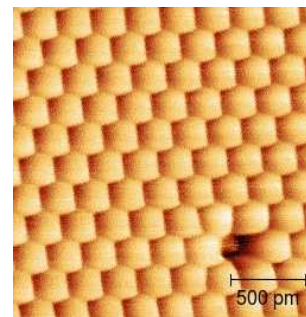
Vertical manipulation: Catch the molecule...

Method: Z spectroscopic curve in the **center** of the molecule

STM Topography

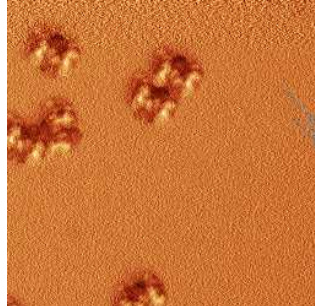


Friction measurement with a molecule linked to the tip

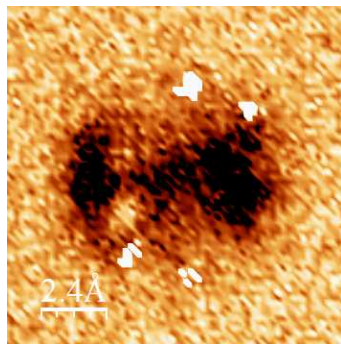


Atomic resolution on Cu(111)

Simultaneous Frequency Shift

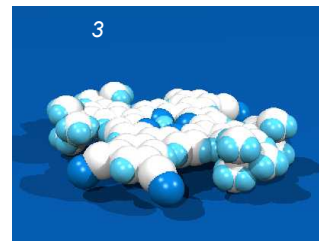
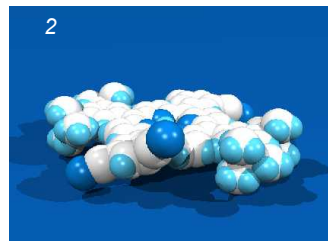
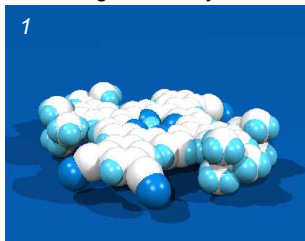
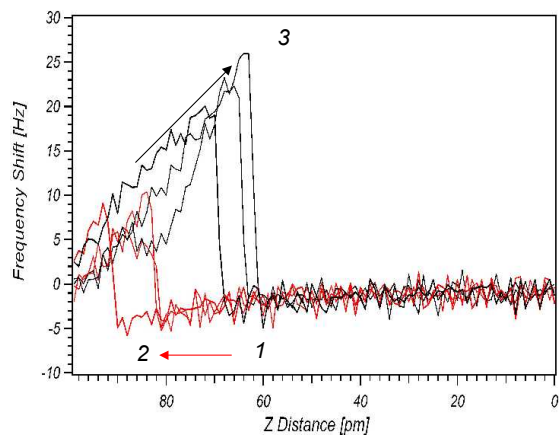


3d-force spectroscopy: Observations of localized instabilities

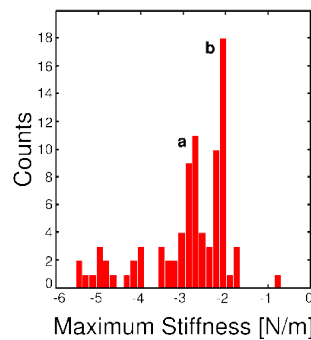
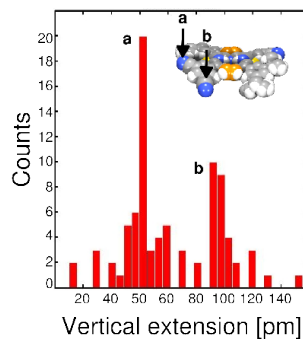
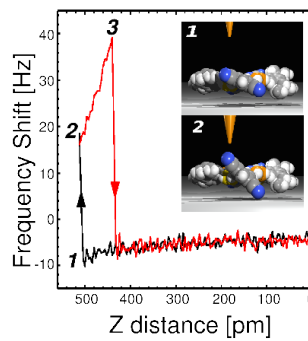
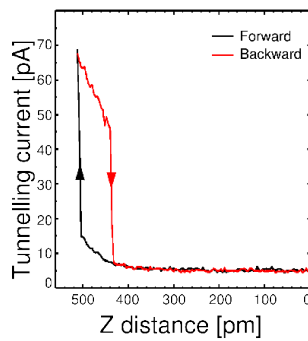


Three-dimensional Force Field Spectroscopy

Origin of the hysteresis



Vertical switching and statistics



Vertical switching:

- Tip-molecule junction between a CN function and the Cu-terminated tip.

- Attractive interaction force (≈ -150 pN) to create the bond.

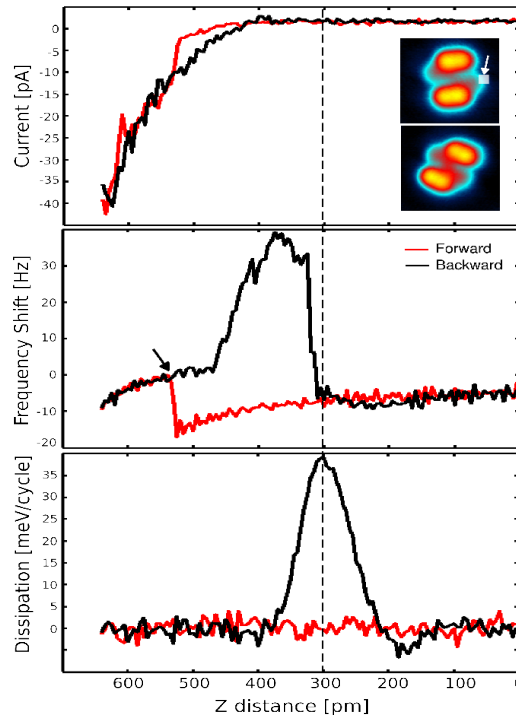
- Possibility to lift the porphyrin leg up by retracting the tip.

- Elastic process independent of the targeted CN functions as well as the enantiomeric form.

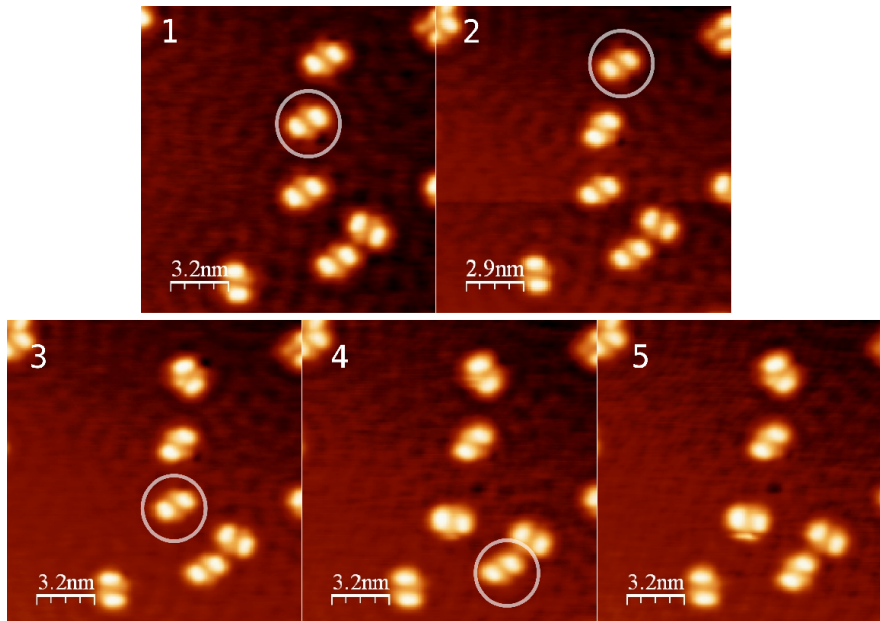
Rotation by controlled force interactions

Rotational switching of the molecule:

- Tip-induced motion of the porphyrin by manipulating the CN function with a single z spectroscopic curve.
- Rotation of 60° with respect to the initial conformation.
- Absolute interaction force = - 500 pN during manipulation, dissipated energy = 30-80 meV/cycle.
- Fully elastic process (no tunnelling current and bias variation).



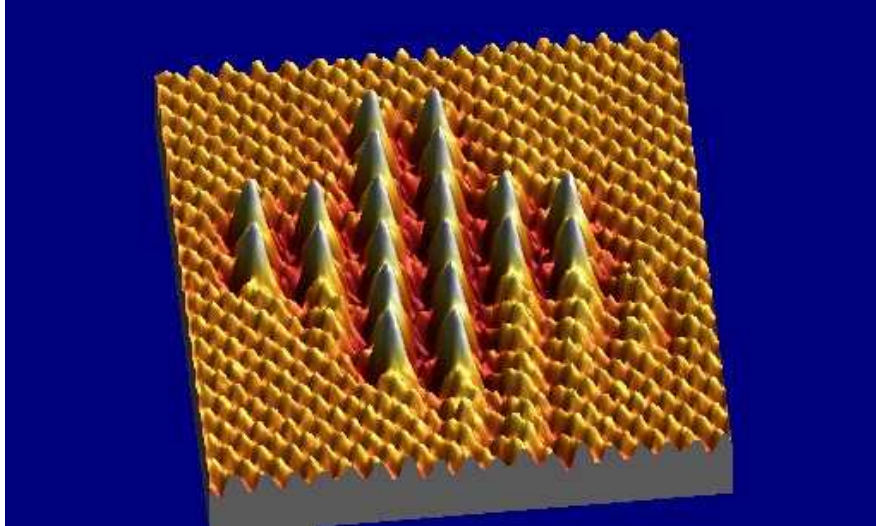
Rotation of molecules clockwise and anticlockwise



= Possibility to rotate molecules in both directions (clockwise and anticlockwise) without consideration to their symmetry

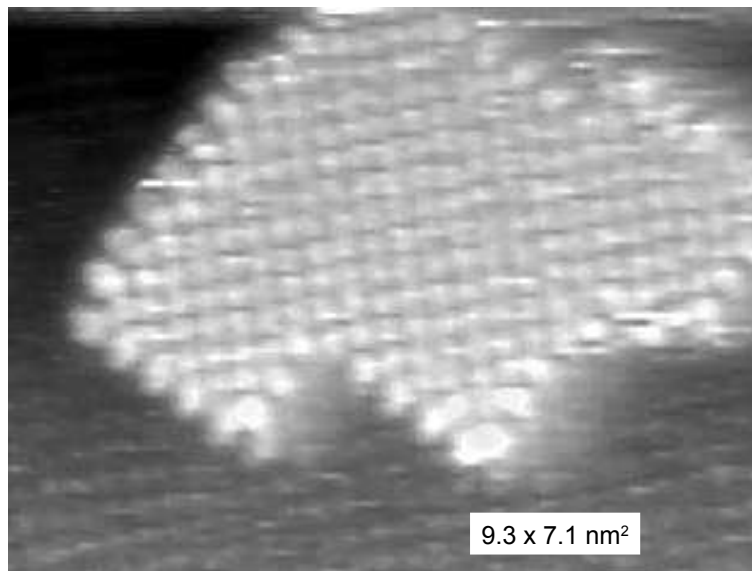


A Small Swiss Cross made by AFM at room temperature torsional resonance imaging



S. Shigeki et al.

Die "Nano-Schweiz"



NaCl-Insel mit AFM abgebildet